



INTEGRATED OPTICS I: SILICON PHOTONICS

SHIRAZ UNIVERSITY

DR. M. MIRI

2015

PHOTONICS AND SILICON PHOTONICS

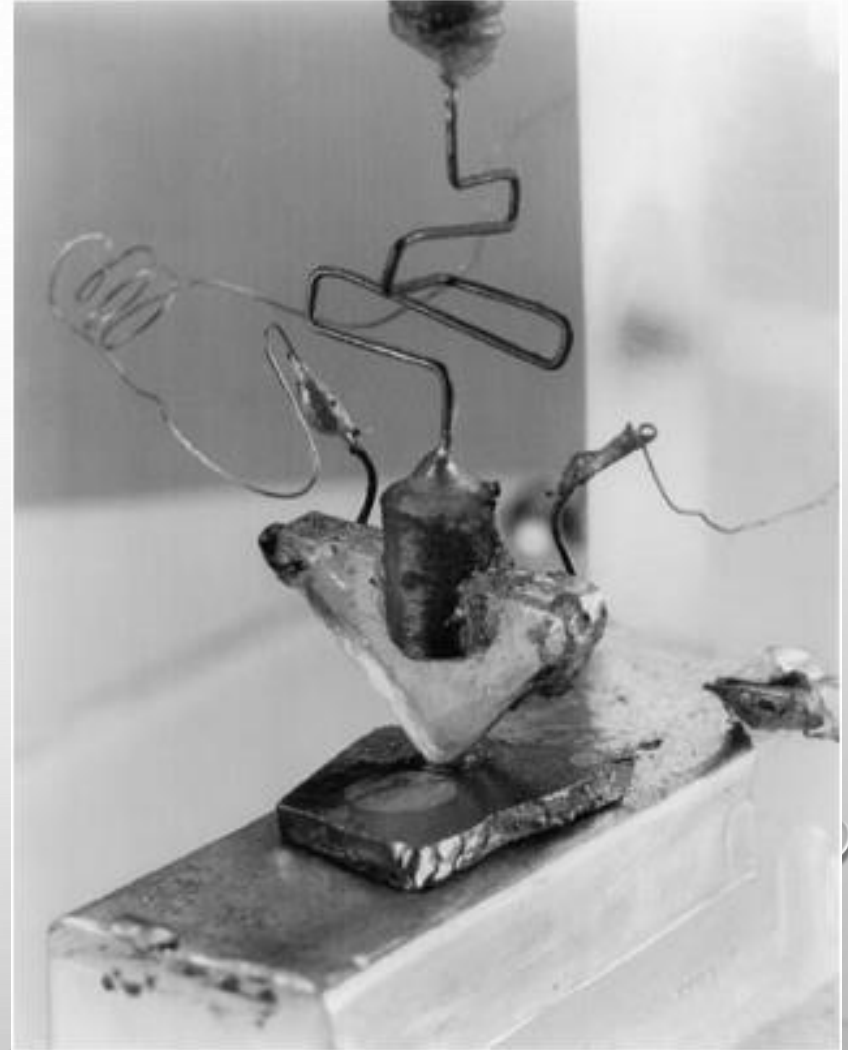
- **PHOTONICS IS THE TECHNOLOGY ASSOCIATED WITH SIGNAL GENERATION, PROCESSING, TRANSMISSION AND DETECTION WHERE THE SIGNAL IS CARRIED BY PHOTONS (I. E. LIGHT)**
- **PHOTONIC DEVICES PRODUCED WITHIN STANDARD SILICON FACTORY AND WITH STANDARD SILICON PROCESSING**

OUTLINE

- **MICROELECTRONIC EVOLUTION**
 - **THREE RULES: SMALLER, CHEAPER, FASTER.**
 - **LIMITATIONS!**
- **OPTICAL COMMUNICATION EVOLUTION**
- **A NEW TECHNOLOGY PLATFORM: SILICON PHOTONICS**
 - **CURRENT STATUS**
 - **EXPECTATIONS**

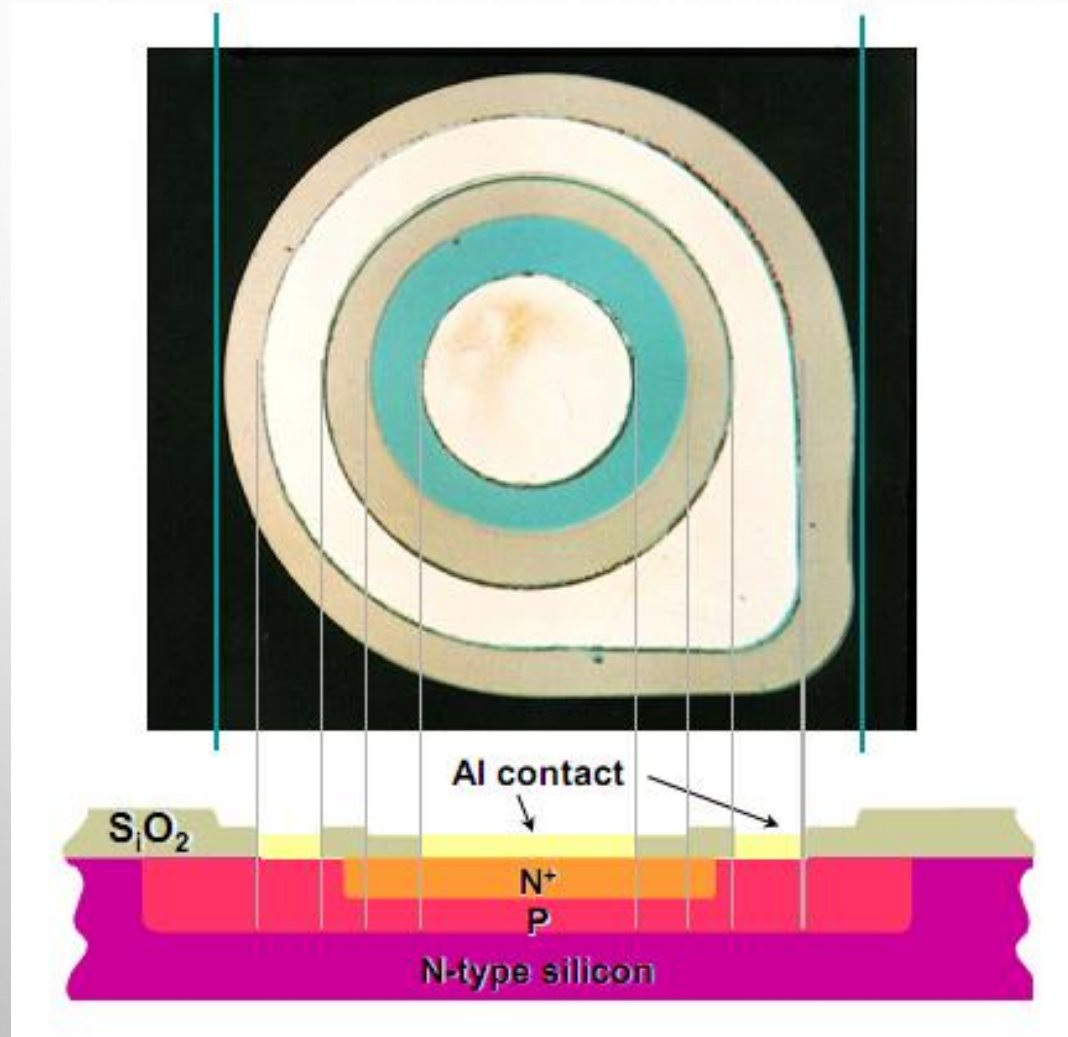
THE INVENTION OF THE TRANSISTOR

- 1947



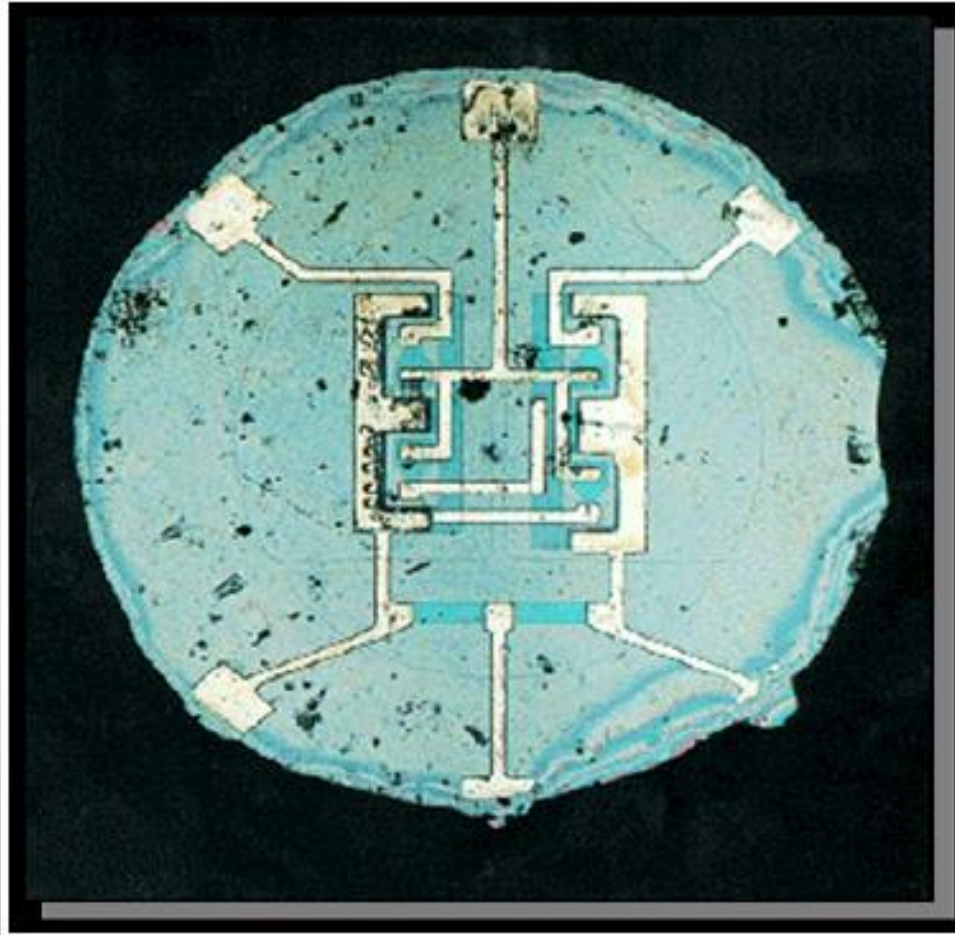
THE FIRST PLANAR TRANSISTOR

- 1959



THE FIRST PLANAR INTEGRATED CIRCUIT

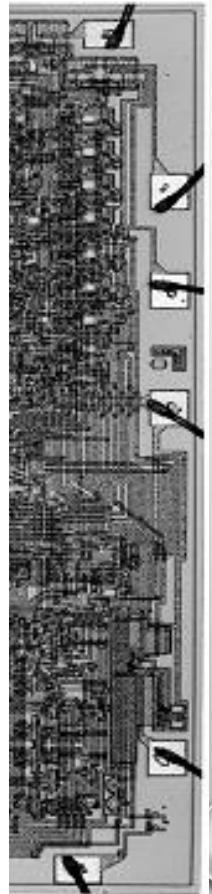
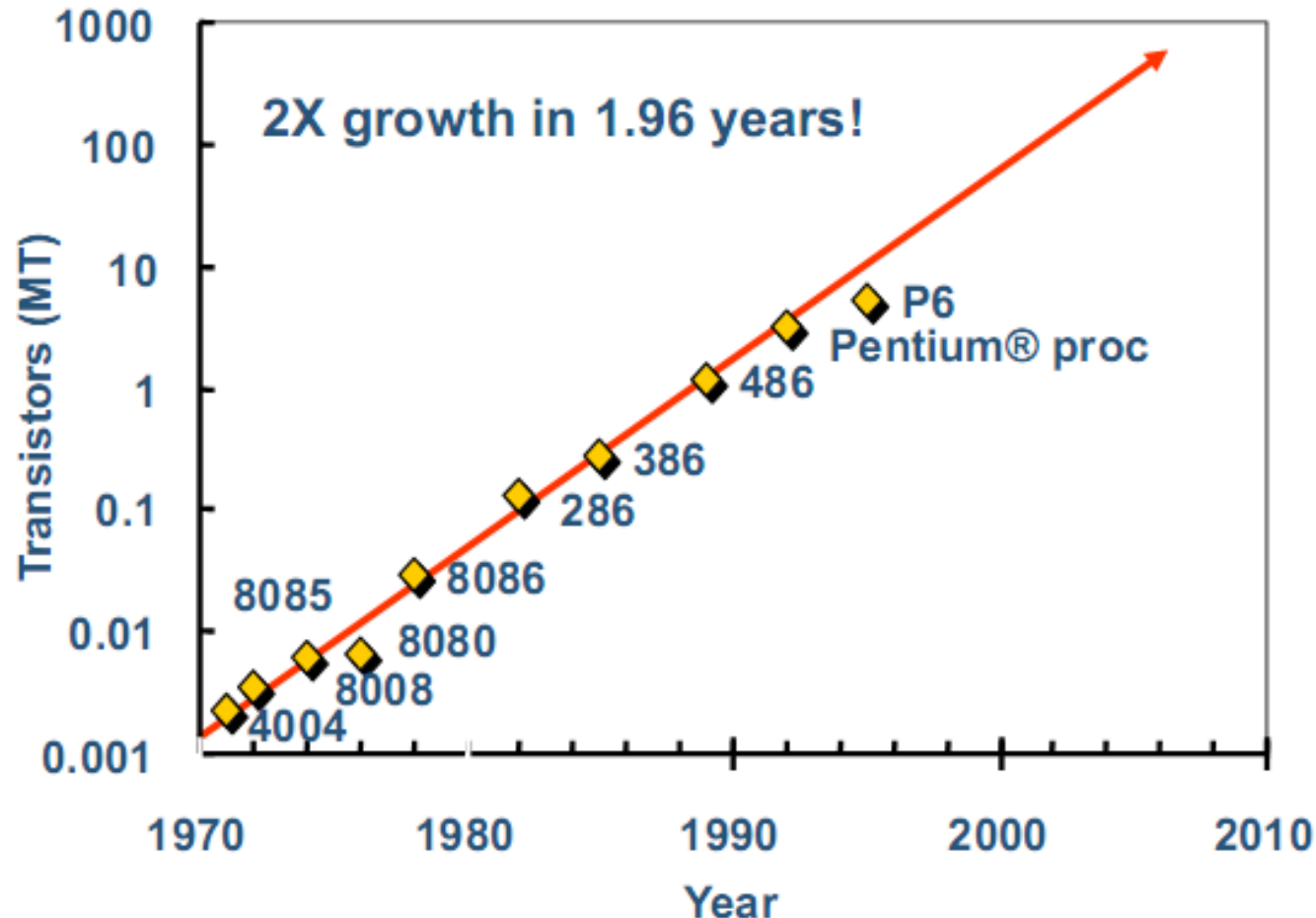
- 1961



MOORE'S LAW

- INTEL

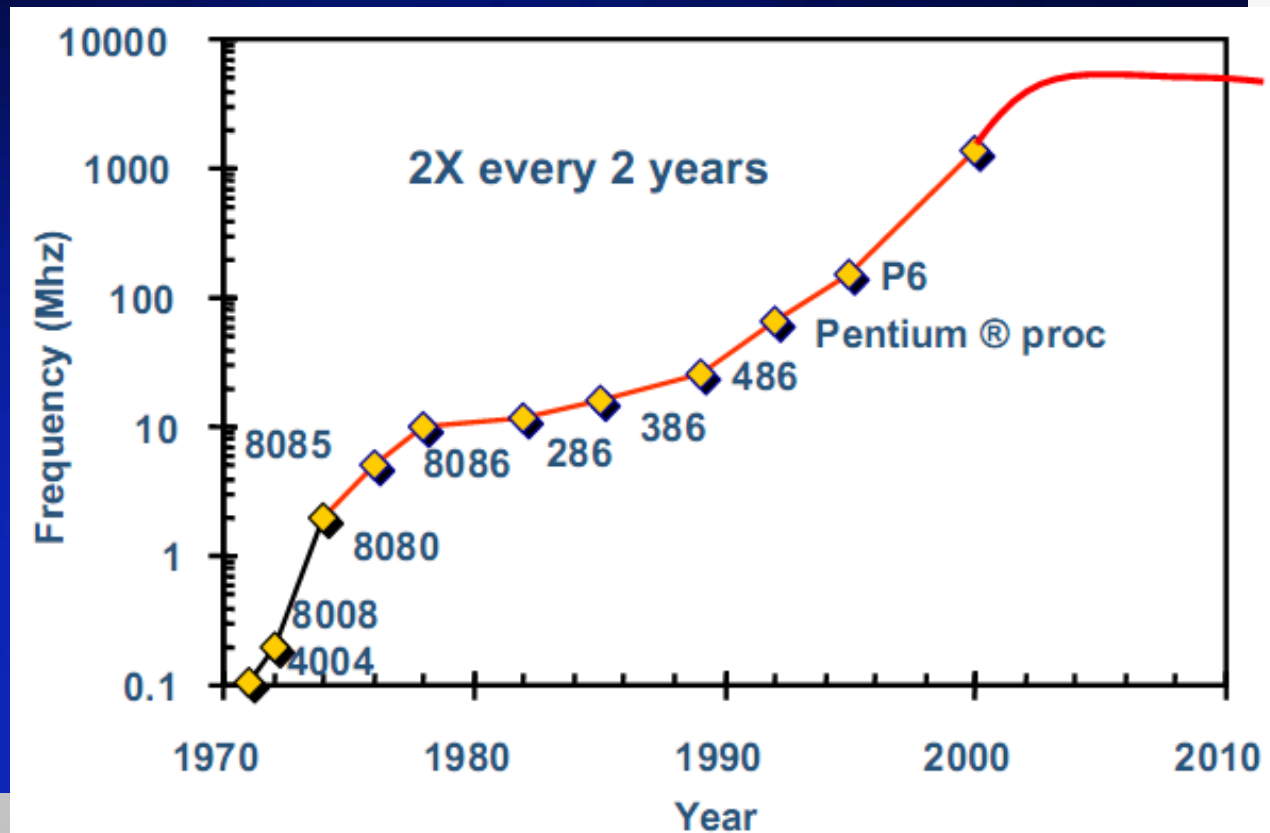
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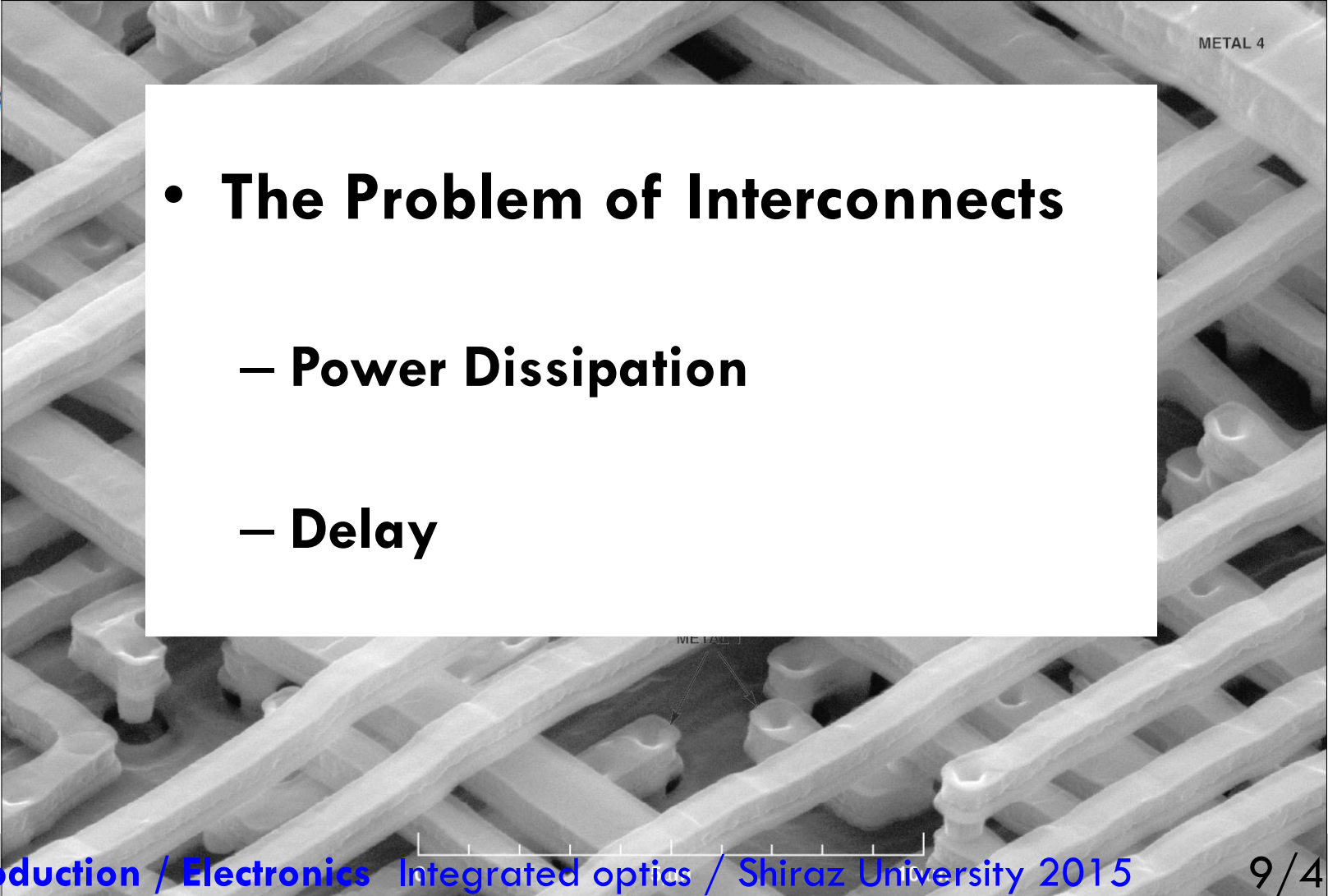
LIMITATIONS OF ELECTRONIC EVOLUTION

- CLOCK F

Gordon Moore Prediction Circa 1977

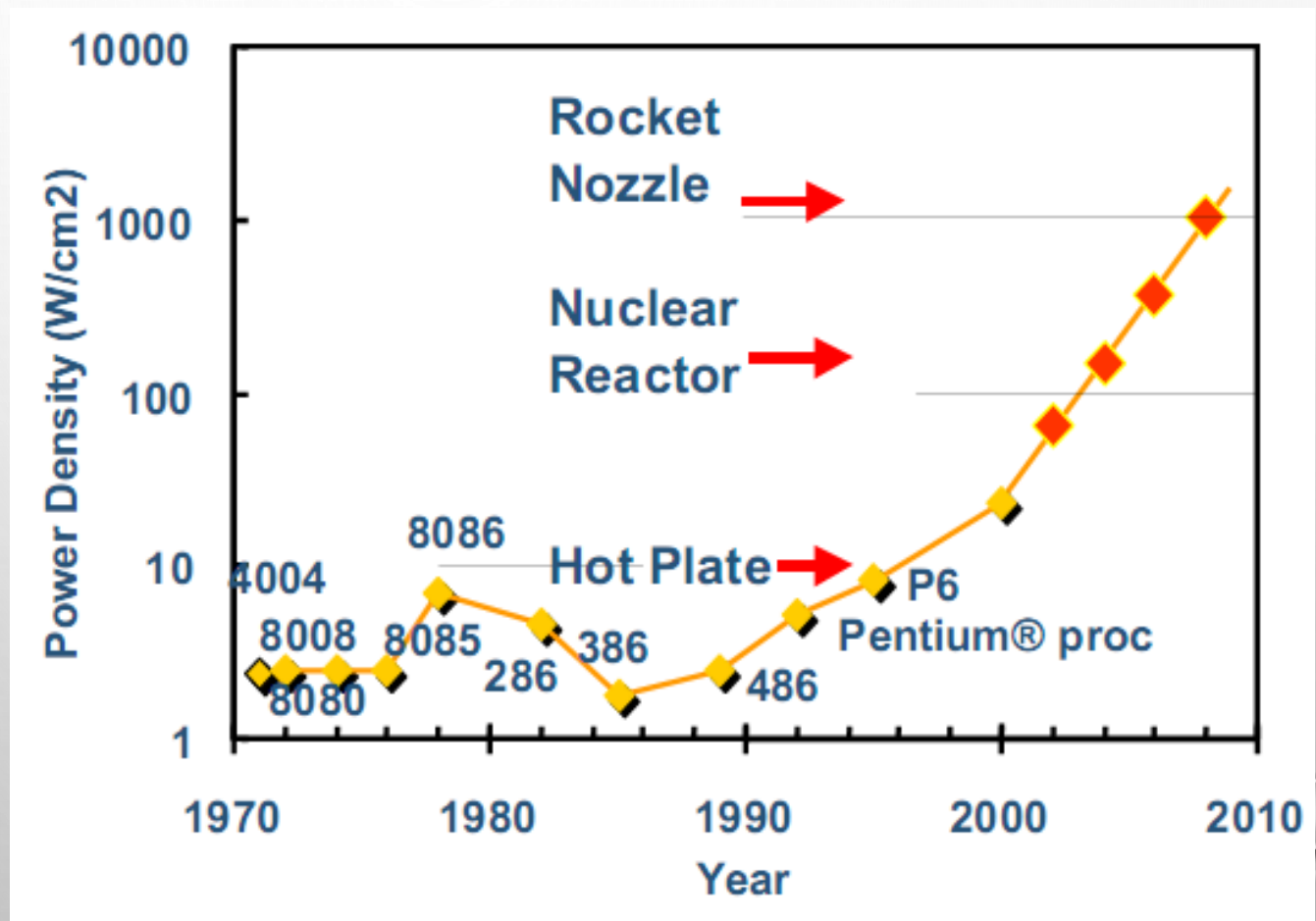


LIMITATIONS OF ELECTRONIC

- 
- **The Problem of Interconnects**
 - **Power Dissipation**
 - **Delay**

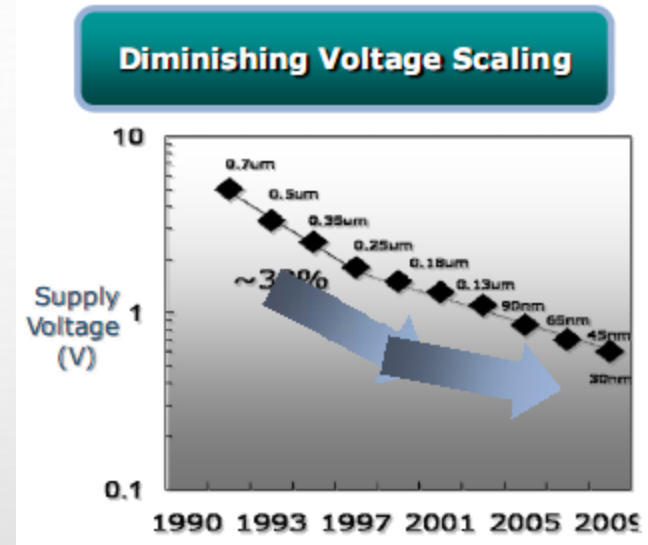
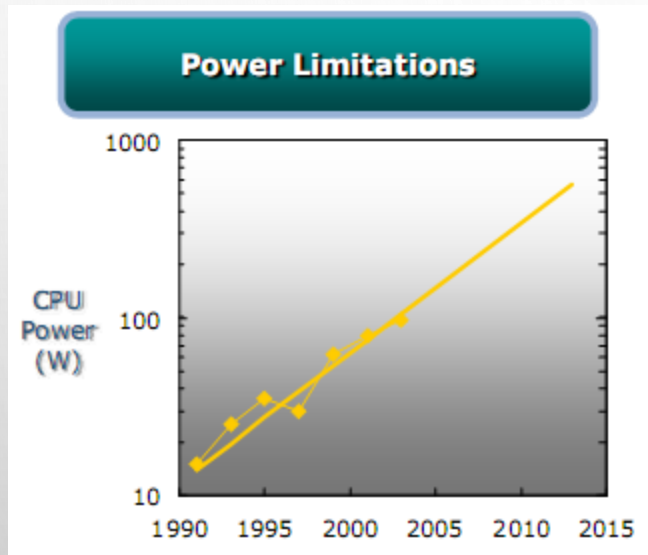
LIMITATIONS OF ELECTRONIC EVOLUTION

- POWER DENSITY



LIMITATIONS OF ELECTRONIC EVOLUTION

- POWER DENSITY



$$\text{Power} = \text{Capacitance} \times \text{Voltage}^2 \times \text{Frequency}$$

also

$$\text{Power} \sim \text{Voltage}^3$$

Silicon Photonics - PhD course prepared within FP7-224112 Helios project



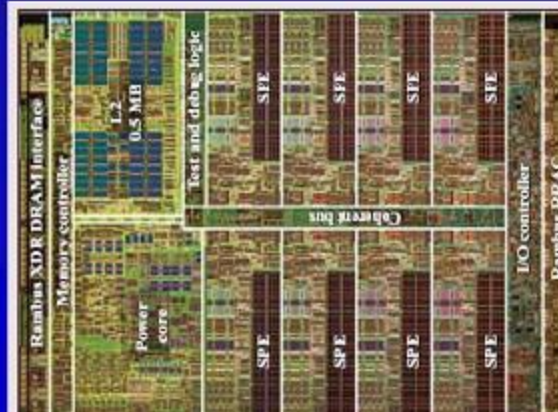
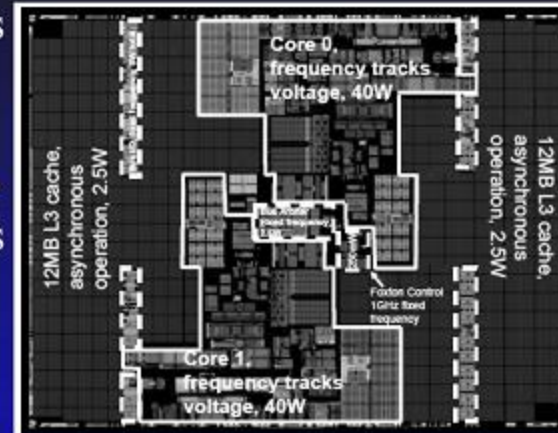
LIMITATIONS OF ELECTRONIC EVOLUTION

The Rise of Multi-Core Architectures

- Rise of parallel multi-core architectures to mitigate power dissipation
- Parallel architectures with multiple simpler processing cores provide **better performance per watt** than architectures based on a single complex processor
- State-of-the-art commercial chips feature **more parallel and distributed architectures** that are essentially multi-core chips
 - Montecito (Intel)
 - Cell (IBM, Toshiba, Sony)
- Key is to design robust, scalable, fast, and power-efficient:

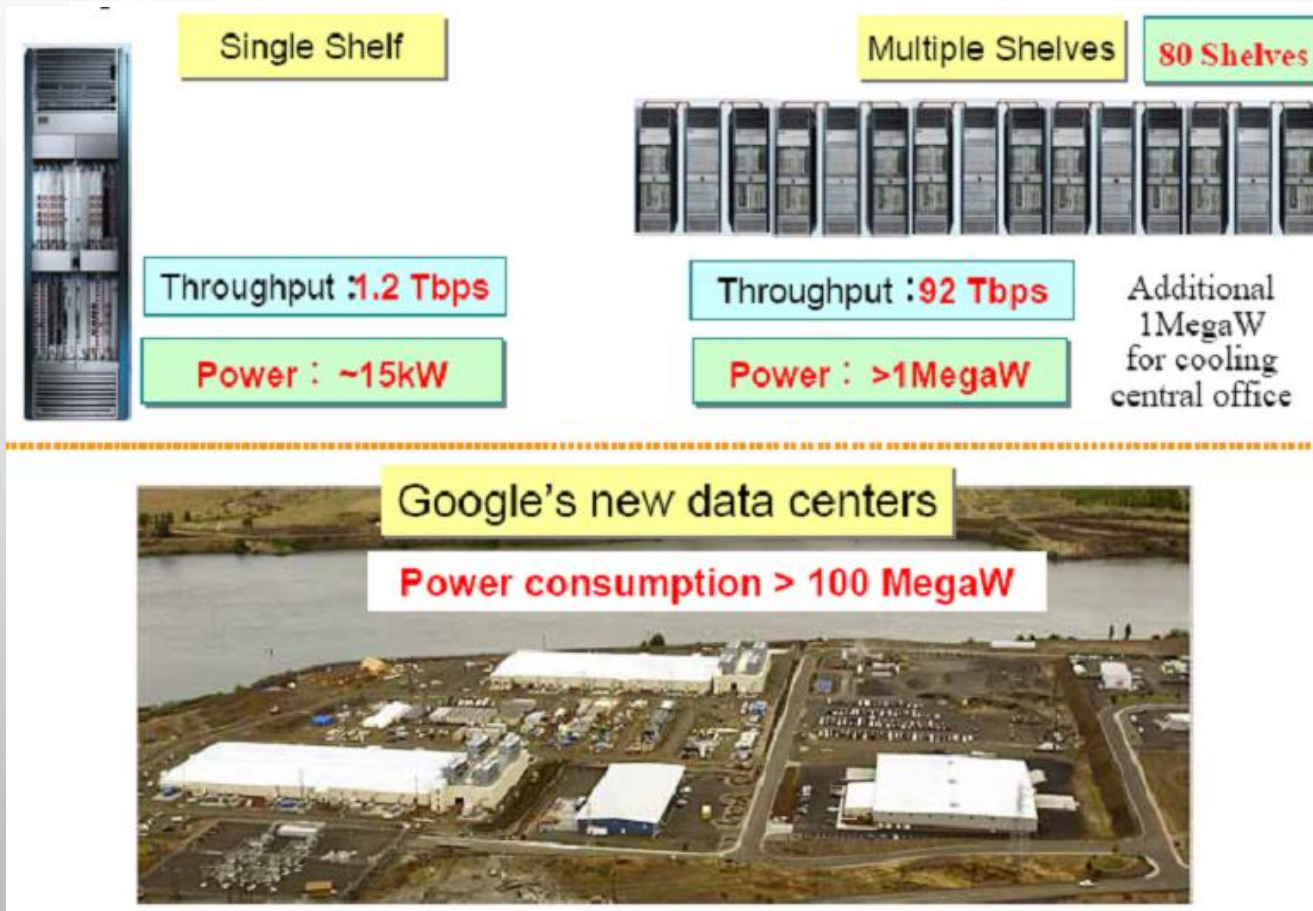
intra-chip communication networks

(58)



LIMITATIONS OF ELECTRONIC EVOLUTION

- INTERCONNECTS POSE PROBLEMS NOT ONLY WITHIN THE CHIP



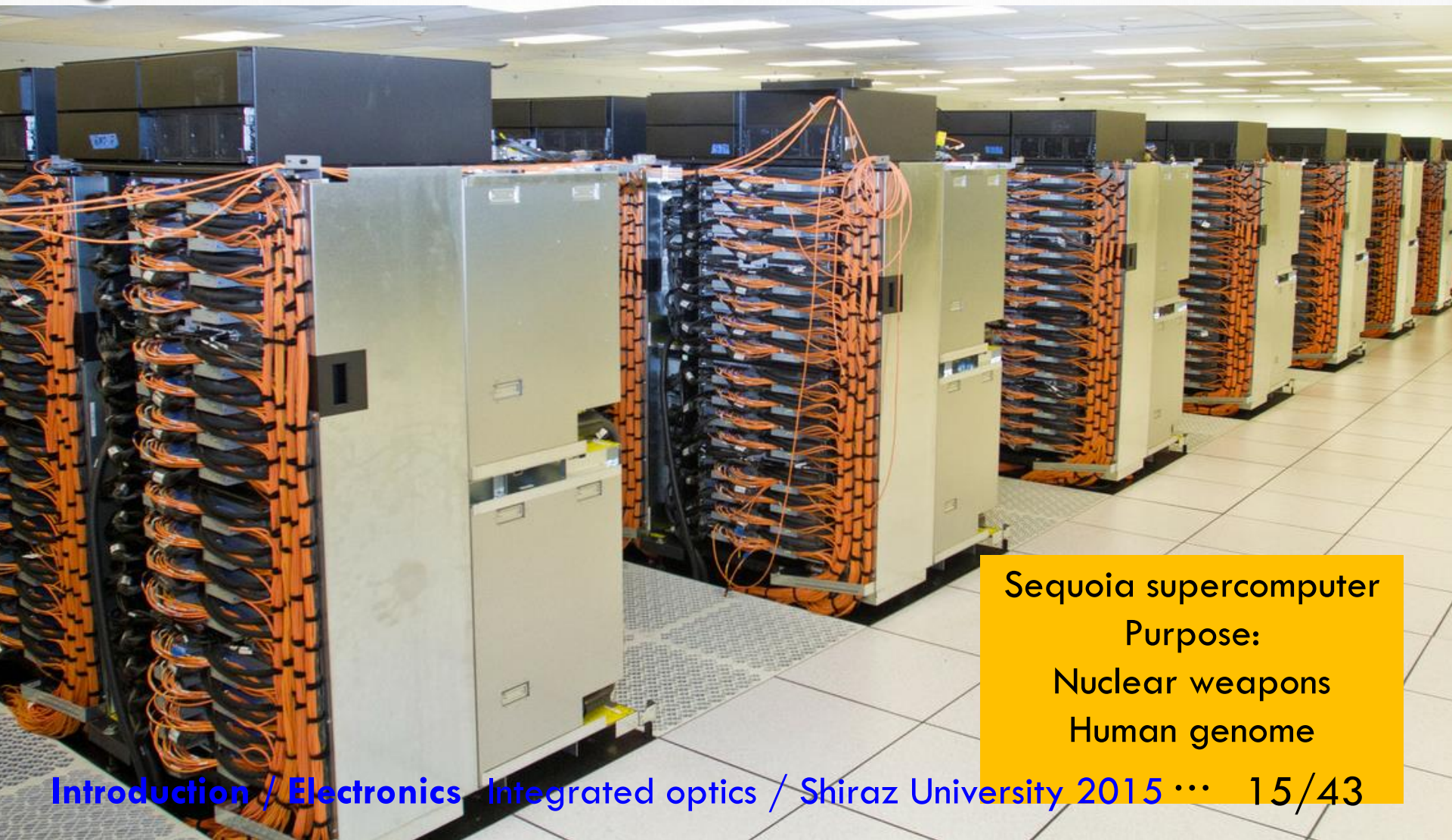
AN EXAMPLE

- **DATA SERVERS AND SUPERCOMPUTERS**

- Facebook datacenter
 - 130,000 m²
 - 65 MW
 - 75% data traffic is inside datacenter



OPTICAL VS. ELECTRICAL DATA COMMUNICATION



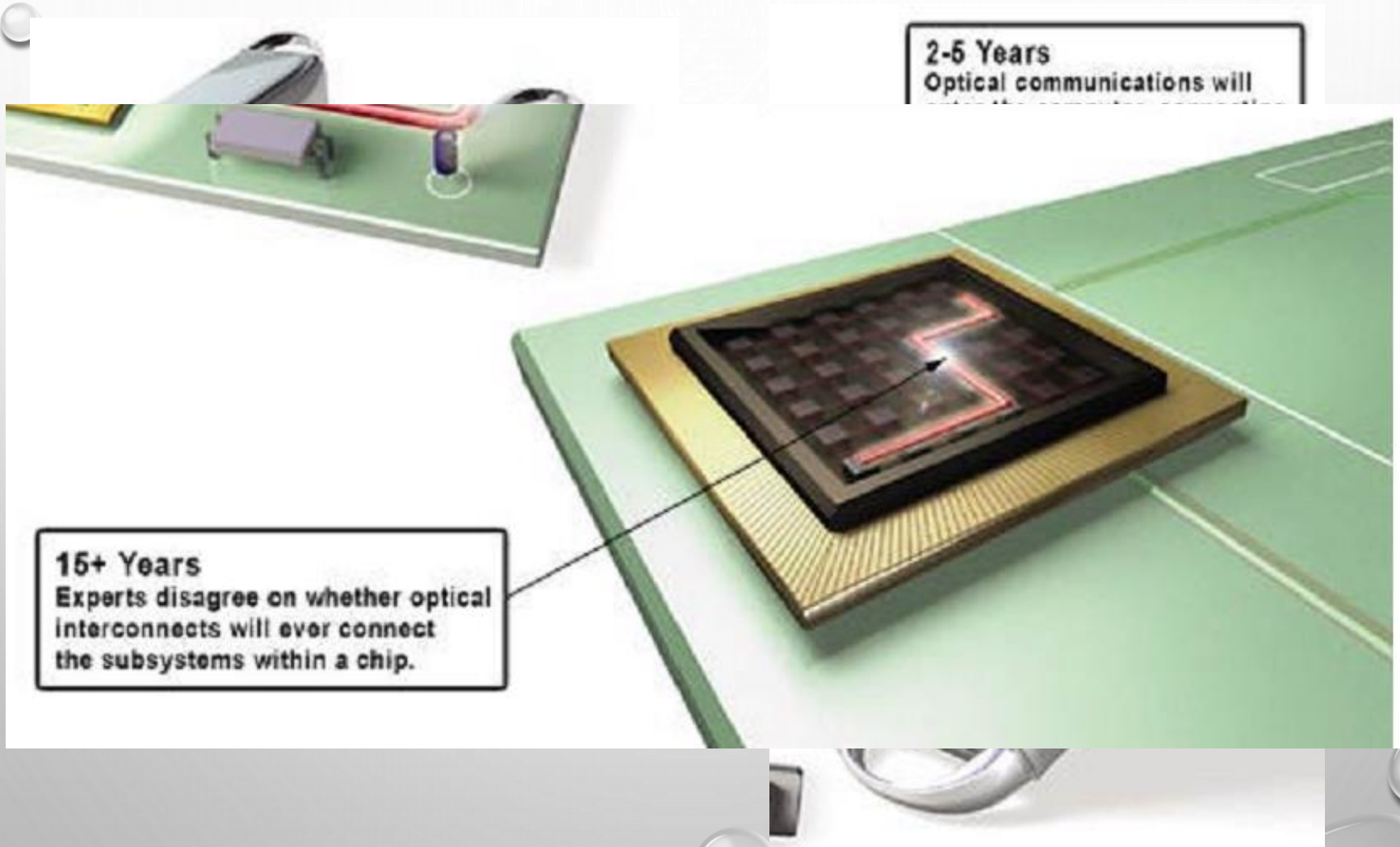
Sequoia supercomputer

Purpose:

Nuclear weapons

Human genome

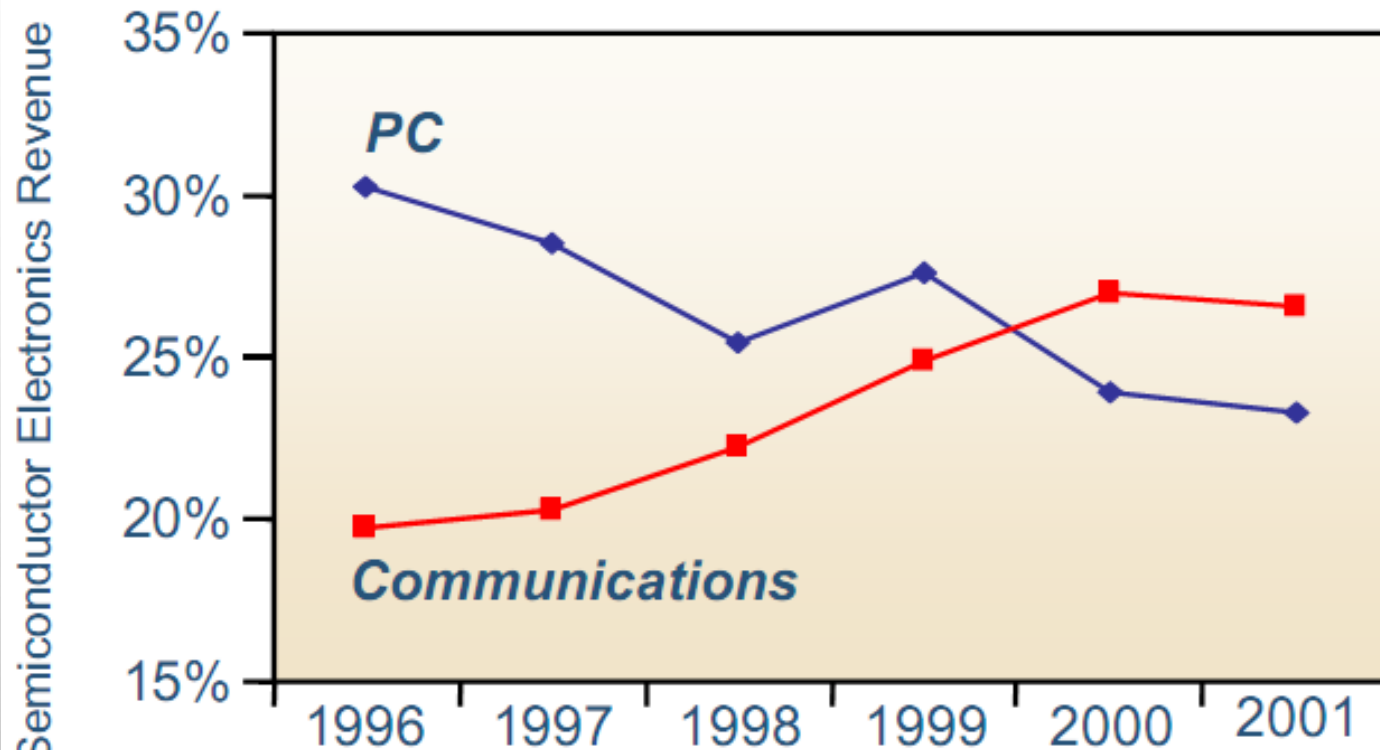
OPTICAL INTERCONNECTS



OPTICAL COMMUNICATIONS: A BRIEF HISTORY

- **1958-59 KAPANY CREATES OPTICAL FIBER WITH CLADDING**
- **1960-TED MAIMAN DEMONSTRATES FIRST LASER IN RUBY**
- **1962-4 GROUPS SIMULTANEOUSLY MAKE FIRST SEMICONDUCTOR LASERS**
- **1970-FIRST ROOM TEMP. CW SEMICONDUCTOR LASER-HAYASHI & PANISH**
- **APRIL 1977-FIRST FIBER LINK WITH LIVE TELEPHONE TRAFFIC**
 - **GTE LONG BEACH 6 MB/S**
- **MAY 1977-FIRST BELL SYSTEM 45 MB/S LINKS 850NM MM**
- **EARLY 1980S-IN-GA-AS-P 1.3 μ M LASERS**
 - **0.5 DB/KM, LOWER DISPERSION-SINGLE MODE**
- **LATE 1980'S-SINGLE MODE TRANSMISSION AT 1.55 μ M, 0.2 DB/KM**
- **1989-ERBIUM DOPED FIBER AMPLIFIER**
- **1996- 8 CHANNEL WDM**

EVOLUTION OF COMMUNICATION



In 2000, for the first time, semiconductor revenues in communication exceeded revenues in PC sector.

WHY SILICON?

- **TRANSPARENT IN 1.3-1.6 UM WAVELENGTH REGION**
- **COMS COMPATIBILITY**
 - **MATURE AND WIDESPREAD TECHNOLOGY**
- **LOW COST**
 - **CHEAPER THAN OTHER SEMICONDUCTORS**
- **HIGH INDEX CONTRAST → SMALL FOOT PRINT**

WHY SILICON?

	Wafer size (R&D)	Wafer size (commercial)	Wafer cost (€)	mm ² substrate cost (€)
Si	450 mm	300 mm	100	0.001
SOI	?	300 mm	800	0.008
InP	150 mm	100 mm	300	0.03
GaAs	200 mm	150 mm	300	0.013

Introduction / Optical Comm. Integ. optics / Shiraz Uni. 2015 20/43

PROBLEMS WITH SILICON

- NO DETECTION IN 1.3 – 1.6 μm BANDWIDTH
 - INDIRECT BANDGAP
- HIGH INDEX CONTRAST
 - → POOR COUPLING
- NO ELECTRO-OPTIC EFFECT
- LACKS EFFICIENT LIGHT EMISSION

SILICON PHOTONICS

- **APPLICATION OVERVIEW**
- **CURRENT STATUS AND PREDICTED NEAR FUTURE**
- **OPTO-ELECTRONIC INTEGRATED CIRCUIT (OEIC)**
- **BUILDING BLOCKS OF OEIC'S**
 - **WAVEGUIDES, WAVEGUIDE/FIBER COUPLERS**
 - **SOURCE AND DETECTOR**
 - **MODULATOR, MULTIPLEXER, DEMULTIPLEXER**

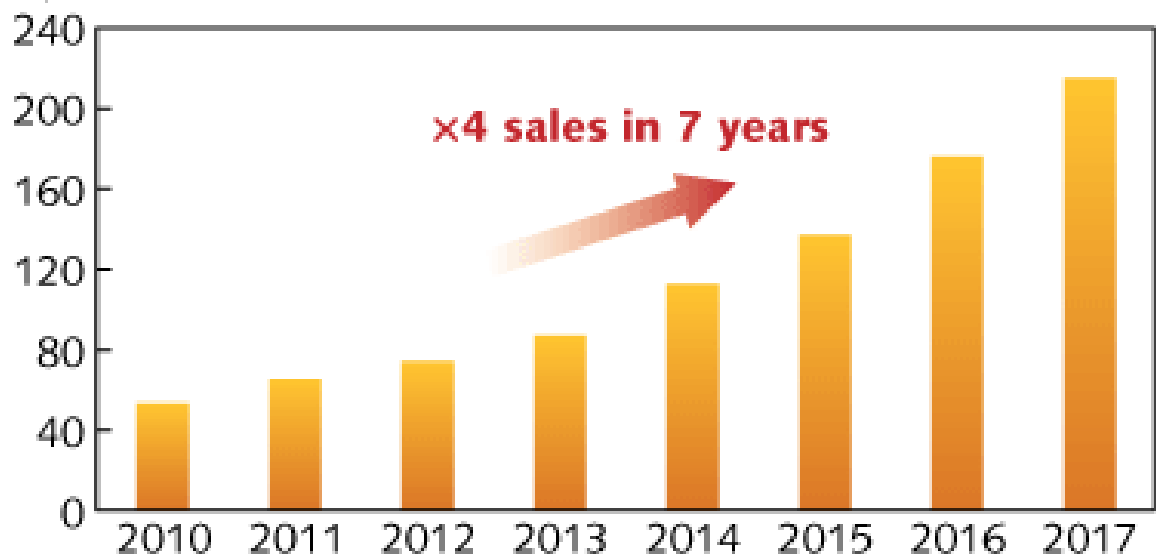
APPLICATIONS

Applications	Examples	Data Rate
Telecom	Used in Metro (1 - 80Km) and long haul applications (40 - 1,000 Km)	10G, 40G, 100G, 400Gbps systems
Datacom	Used in data centers (<1m - 2Km) and campus applications (1 - 5Km)	10G, 25G, 40G, 100Gbps interconnects between systems
Consumer	Connecting desktop PC devices and PCs with HDTVs	5G - 50Gbps
HPC & Data Centers	One High Performance Computer “supercomputer” may consume 40,000 AOCs or 250,000 mid-board modules	Up to 100 Gbps
Commercial Video	Digital signage, digital cinemas, video recording and studios; 4xx2K displays and recording equipment	10G - 50Gbps interconnects
Metrology and Sensors	Measurement of time, temperature, sound, frequency, and stress, range	Typically low data rates but using special silicon photonics sensors
Medical	DNA, glucose, molecular and cellular analysis, etc.	Typically low data rates but using special silicon photonics Sensors
Military / Aerospace	Used in scientific instruments at corporate and national labs; aircraft, space, missiles, radar, imaging and intelligence applications.	High

CURRENT STATUS AND FUTURE

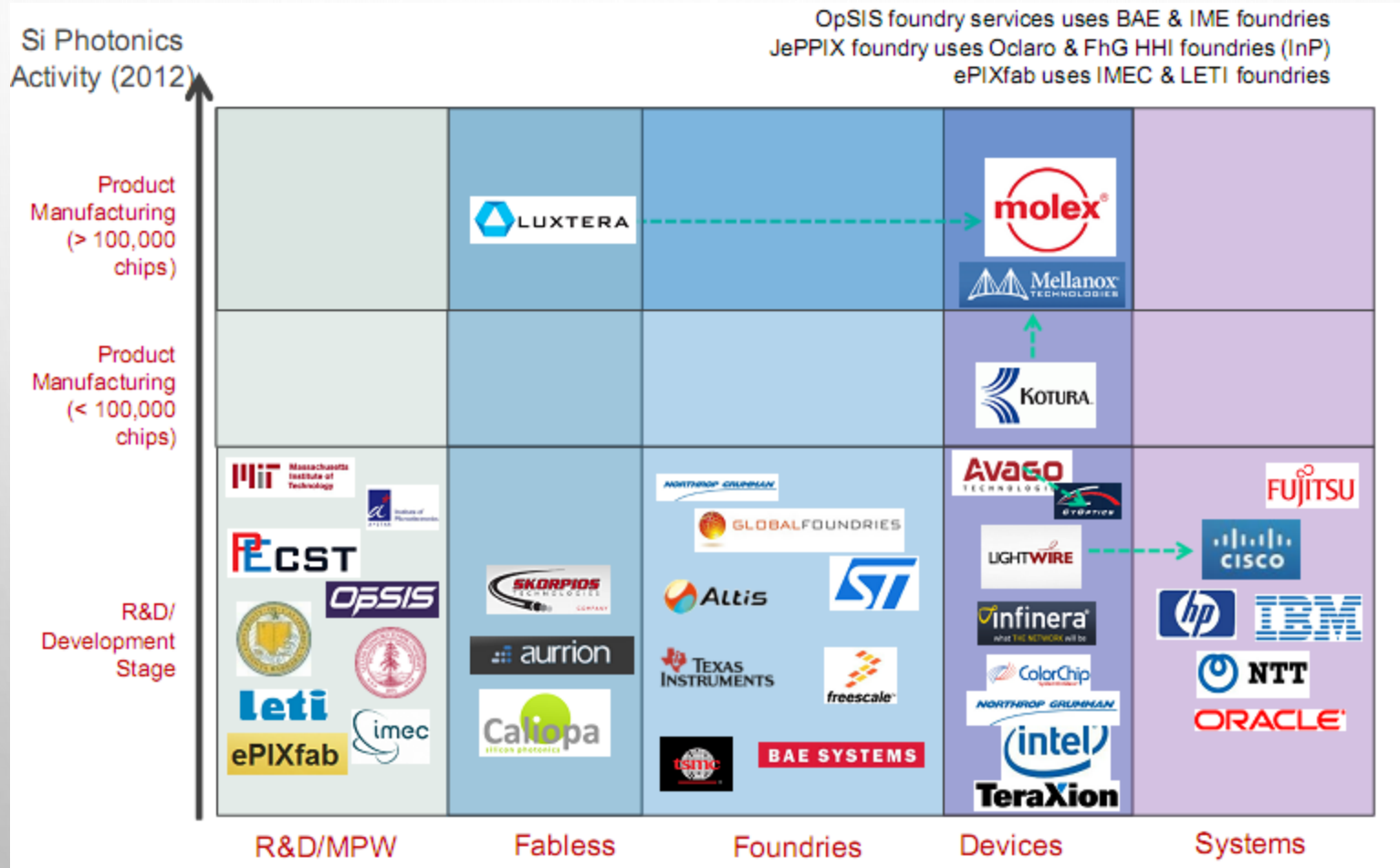
- SILICON PHOTONICS MARKET

Si photonics market (US\$M)



Source: Silicon Photonics: Big Investments, Small Business report, Yole Développement, October 2012

PLAYERS

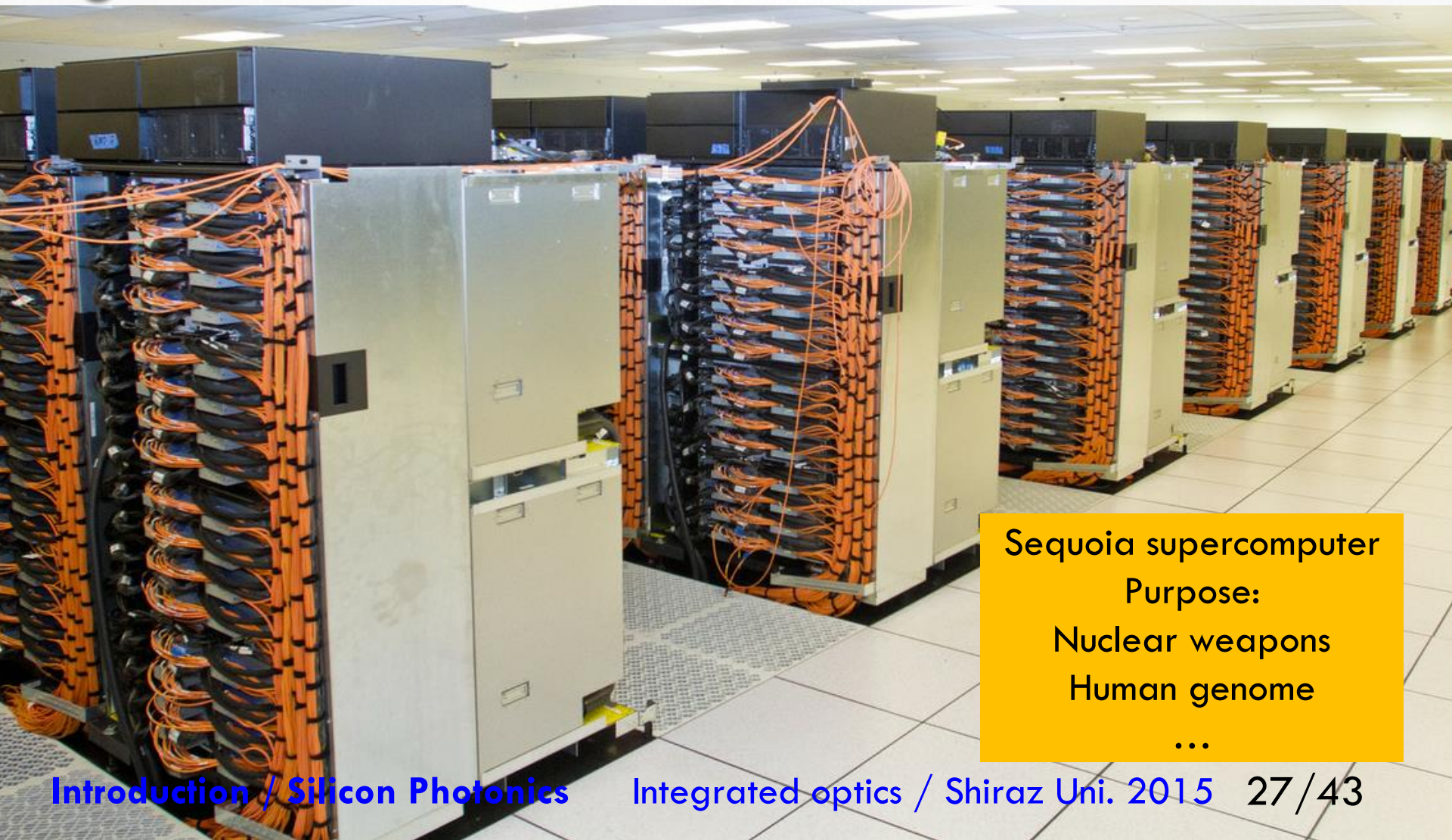


AN EXAMPLE OF APPLICATIONS

- Facebook datacenter
 - 130,000 m²
 - 65 MW
 - 75% data traffic is inside datacenter



OPTICAL VS. ELECTRICAL DATA COMMUNICATION



Sequoia supercomputer

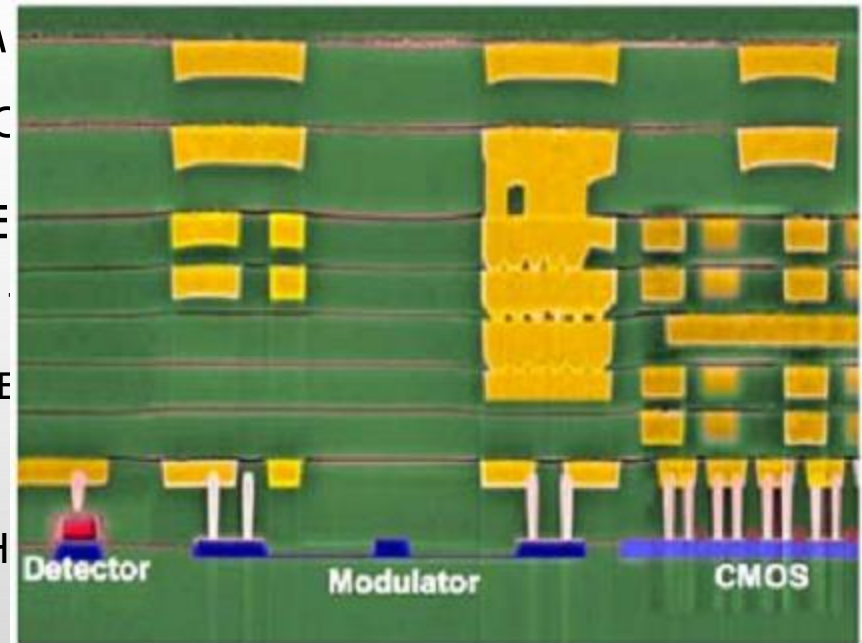
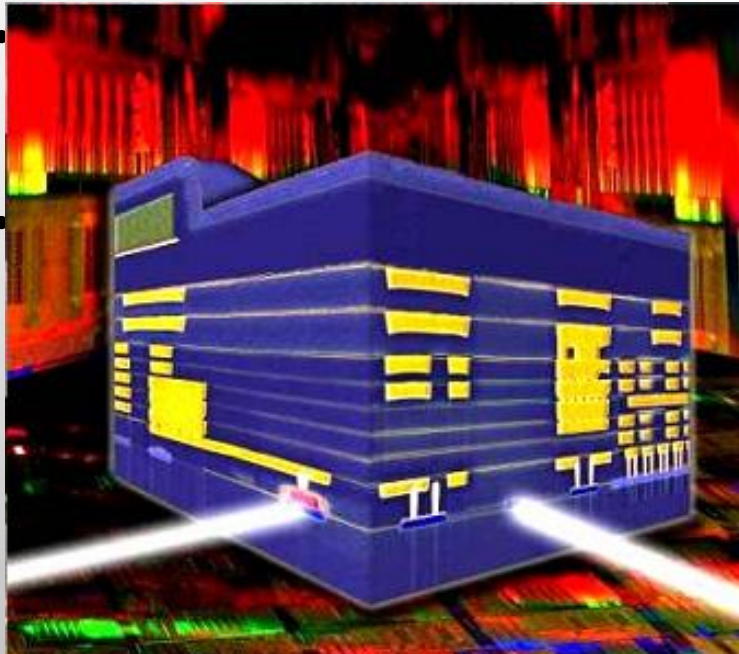
Purpose:

Nuclear weapons

Human genome

...

CURRENT TECHNOLOGY



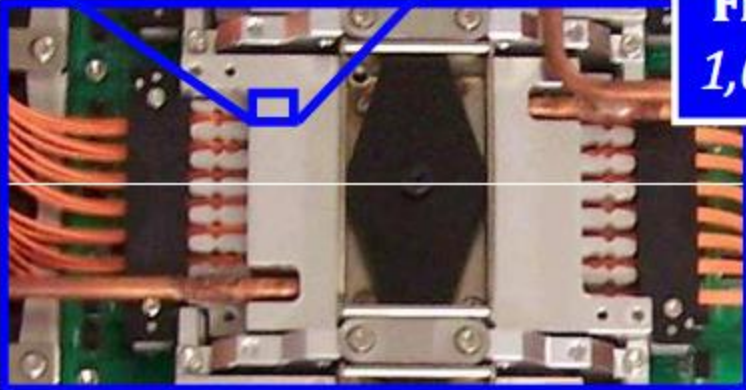
CURRENT TECHNOLOGY



microPOD™ parallel
optical TX/RX

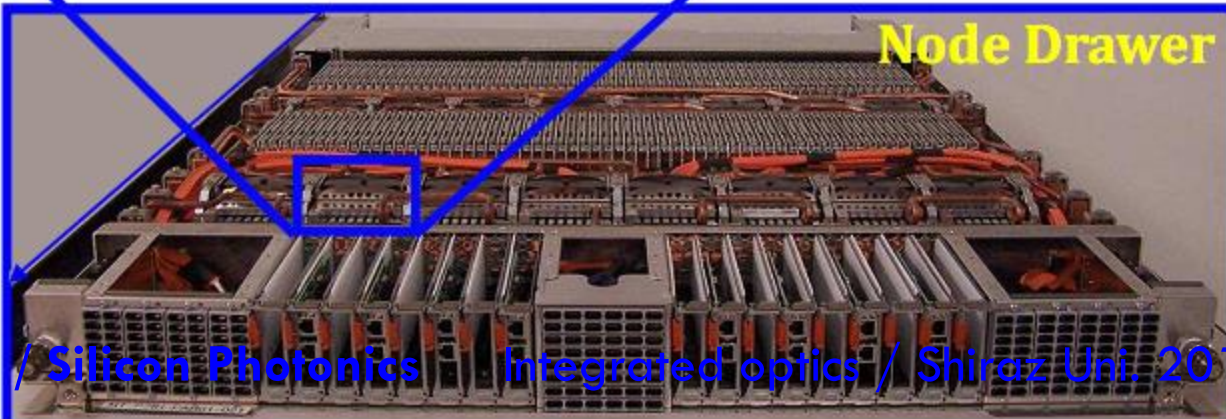
[M. Fields, Avago, OFC 2010, paper OTuP1]

Fiber to the Module
1,000,000 optical links



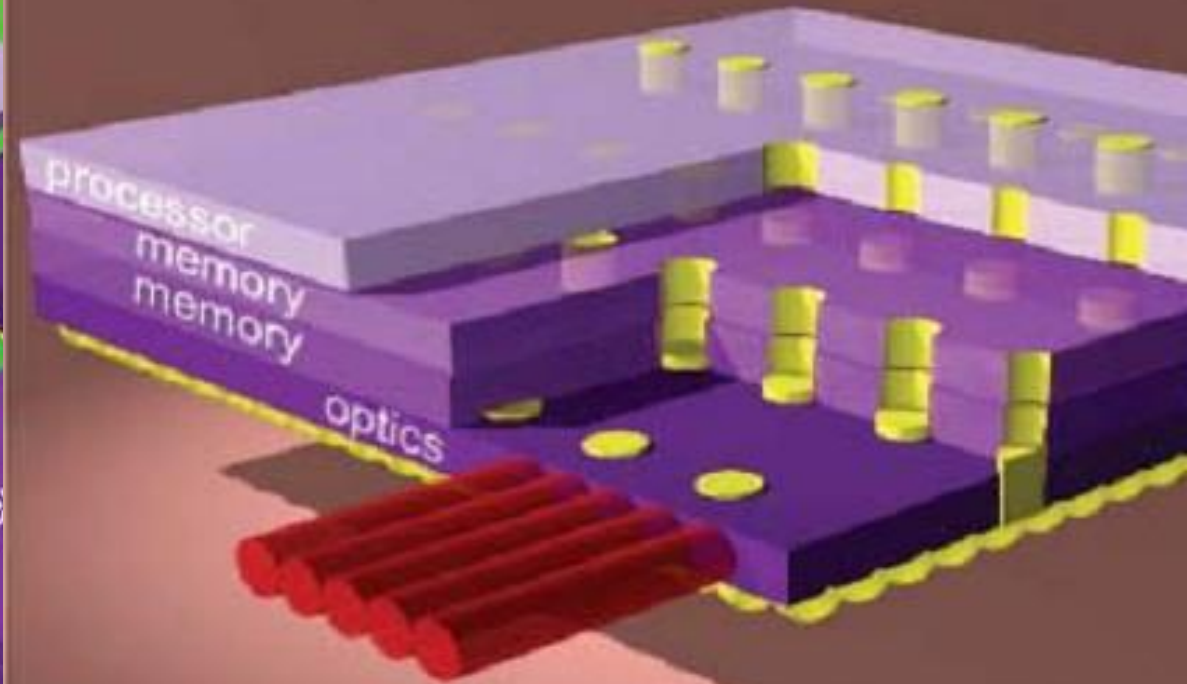
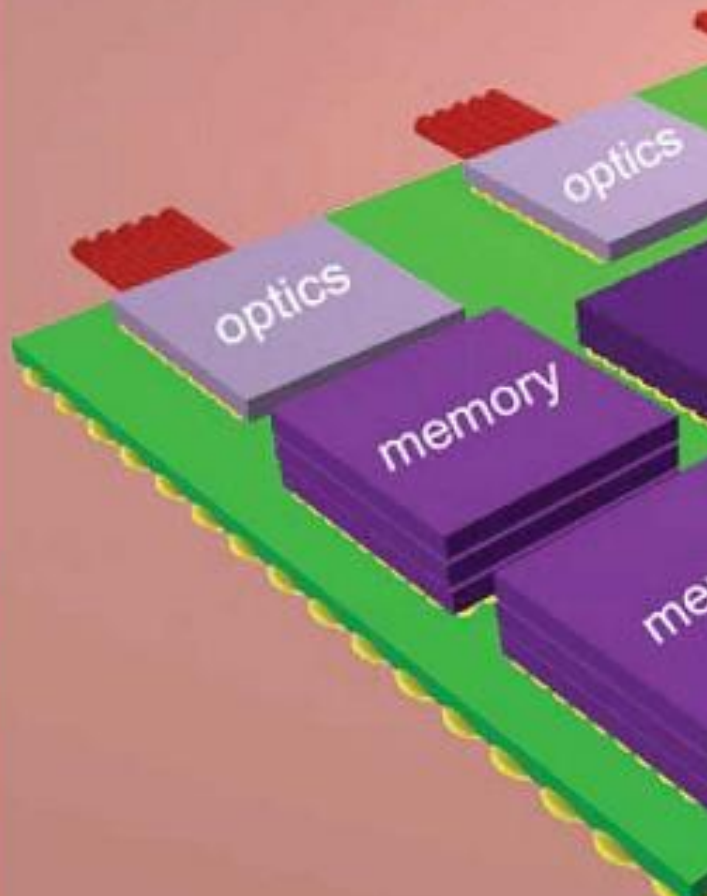
Hub/switch
module, with IC
and 56 microPODs

Node Drawer



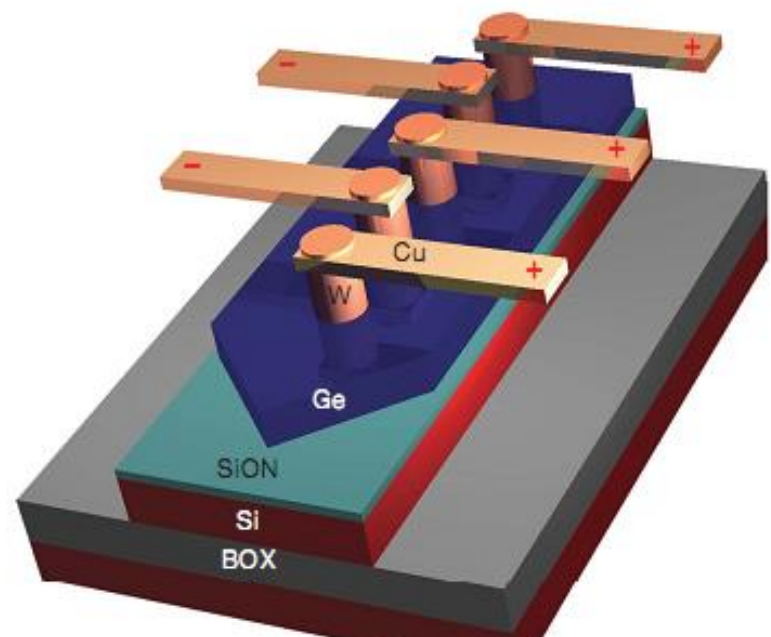
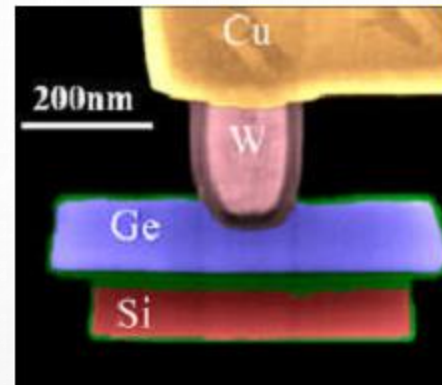
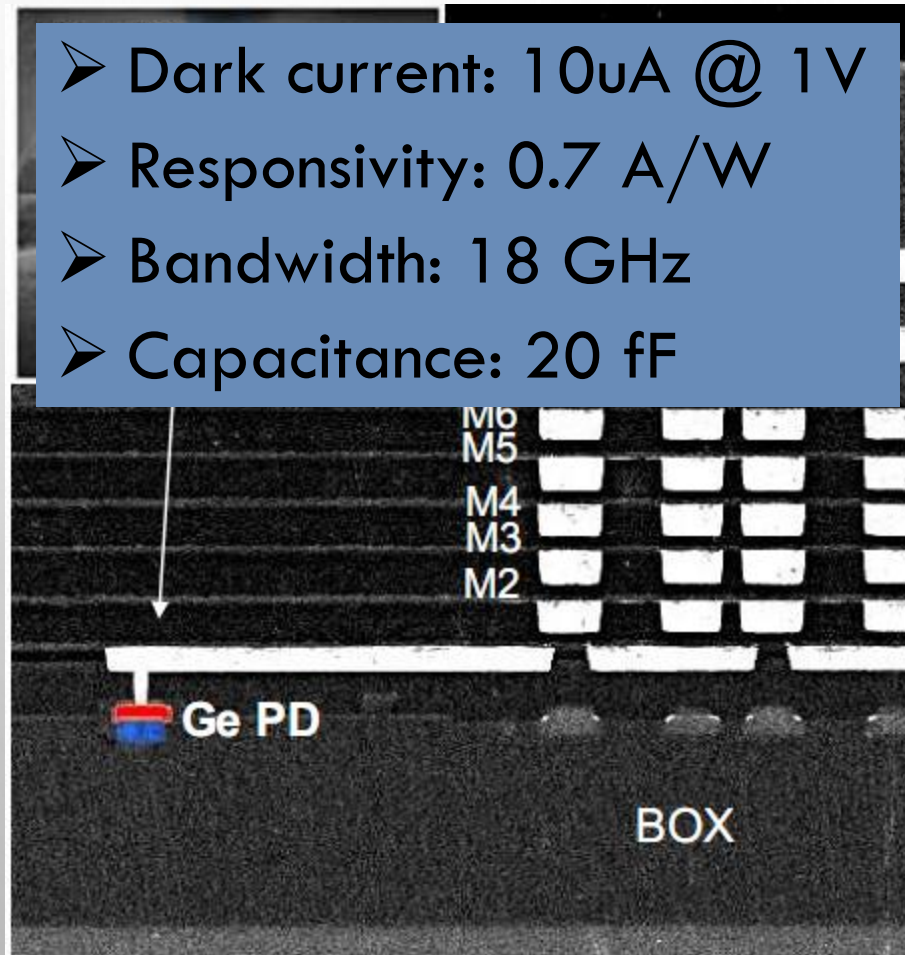
INTEGRATED PHOTONIC ELECTRONIC CIRCUIT

- **Future**



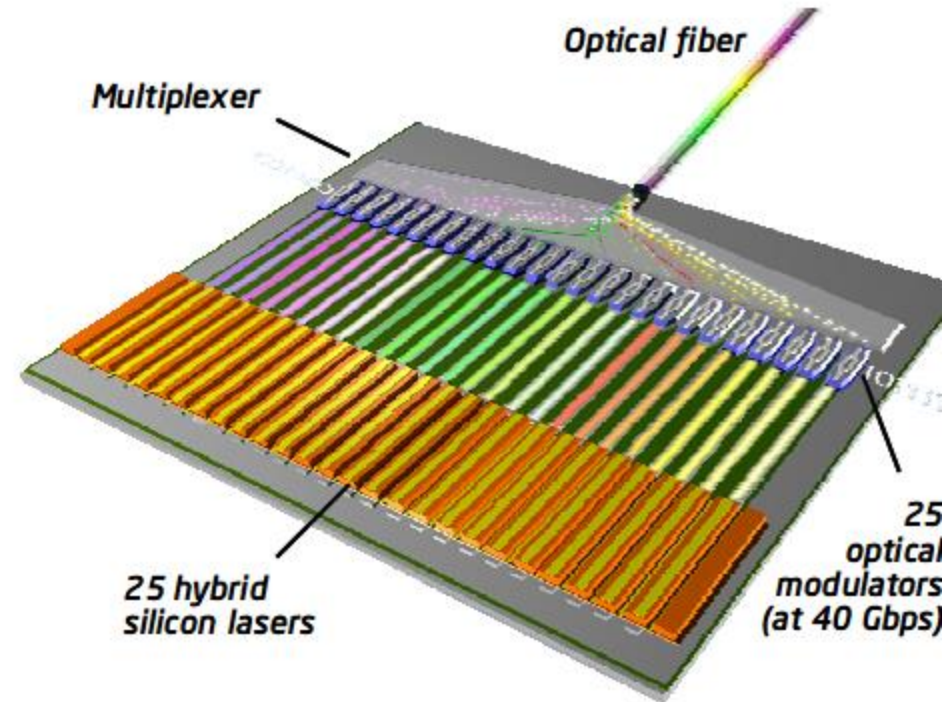
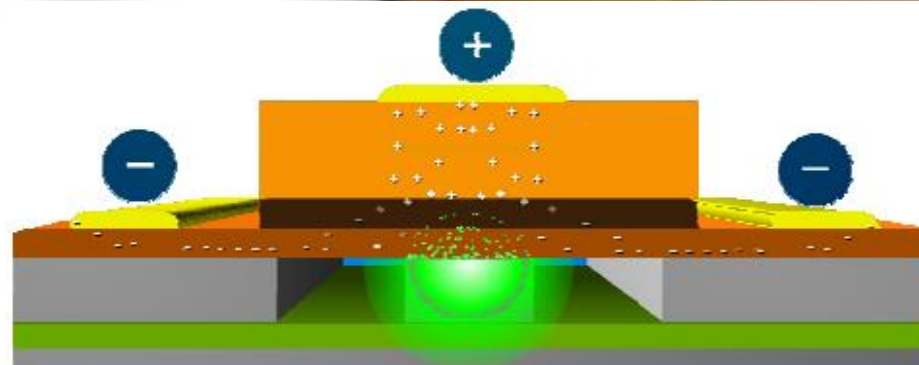
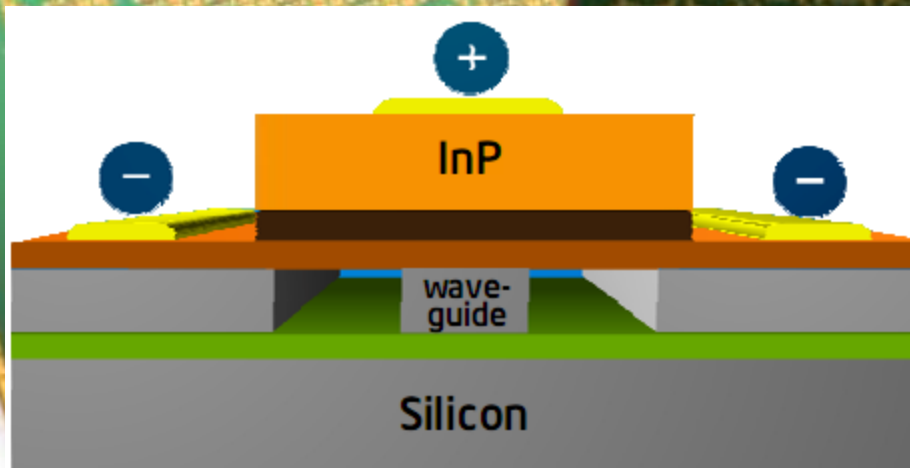
SILICON COMPATIBLE DETECTOR

- Dark current: 10 μ A @ 1 V
- Responsivity: 0.7 A/W
- Bandwidth: 18 GHz
- Capacitance: 20 fF



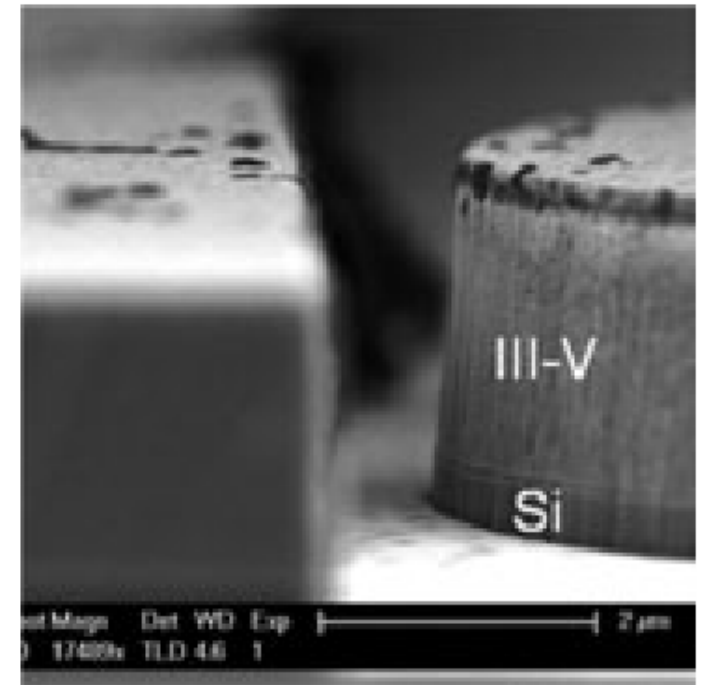
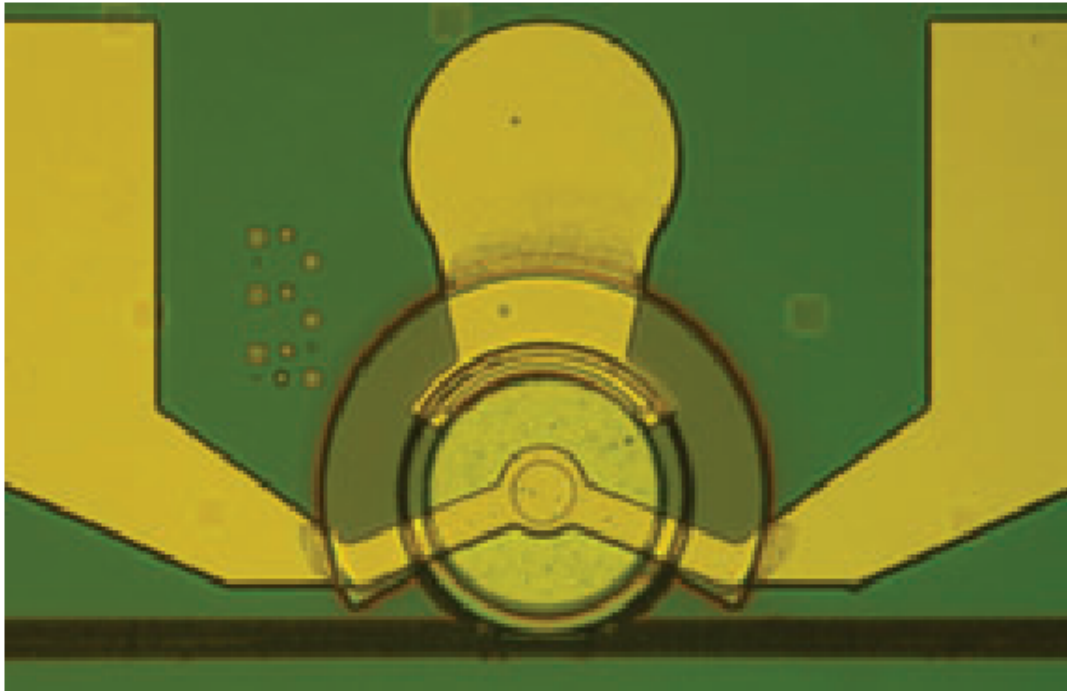
Hybrid Silicon Laser

- Silicon / III-V bonded wafers



HYBRID SILICON LASERS

[Microring lasers]



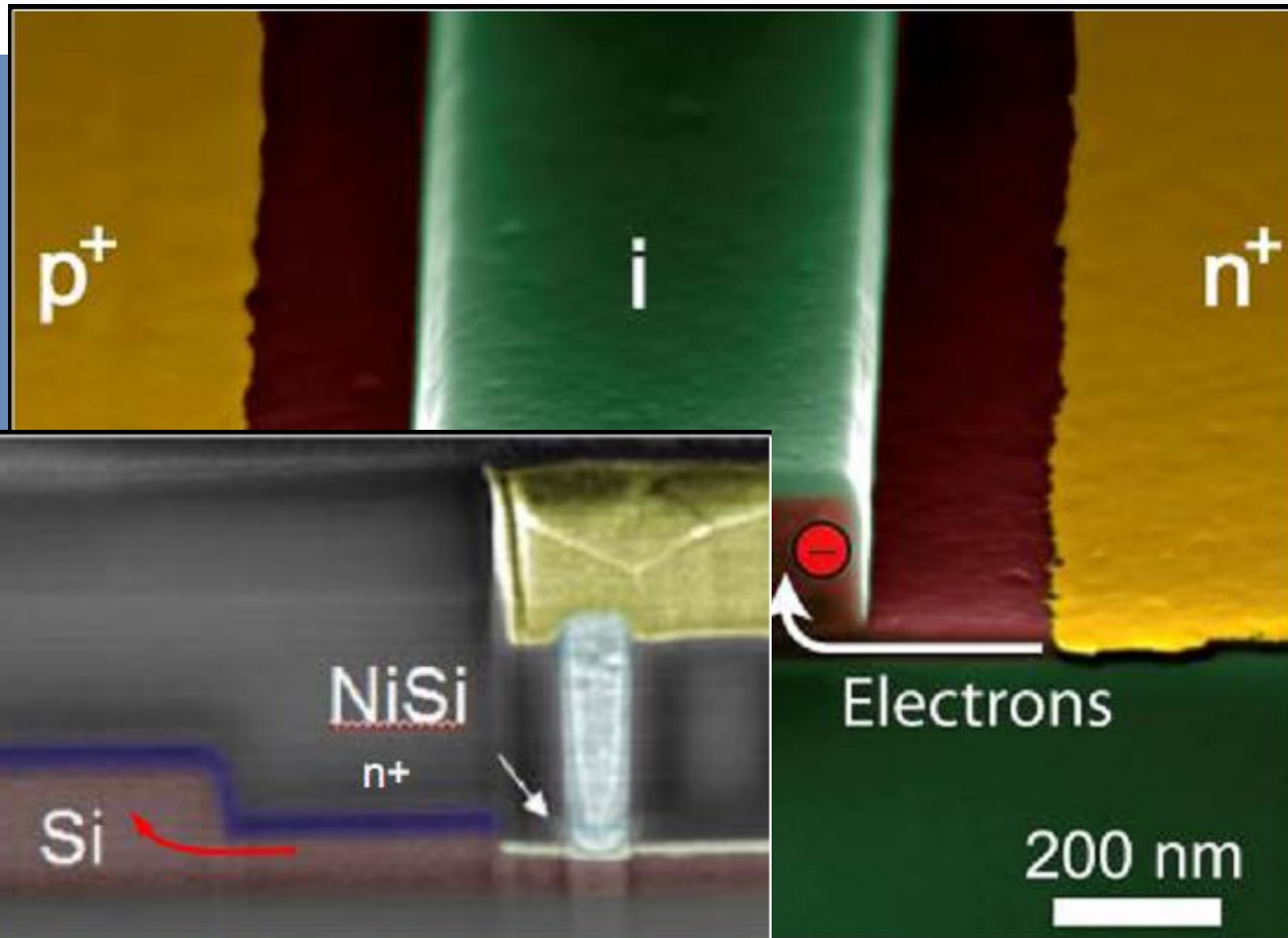
(Left) Photo of a hybrid silicon microring laser. (Right) SEM image of ring and output coupler.

SILICON PHOTONICS MODULATOR

- MODULATION MECHANISMS
 - ELECTRO-OPTICAL REFRACTIVE INDEX CHANGE DUE TO:
 - FREE CARRIER INJECTION IN FORWARD BIASED SI PIN STRUCTURE
 - CARRIER ACCUMULATION IN REVERSED BIASED PIN STRUCTURE
 - CARRIER ACCUMULATION IN MOS CAPACITOR STRUCTURE
- MODULATOR STRUCTURES
 - MZI STRUCTURE
 - COUPLED WAVEGUIDE RING RESONATOR STRUCTURE

SILICON PHOTONICS MODULATORS

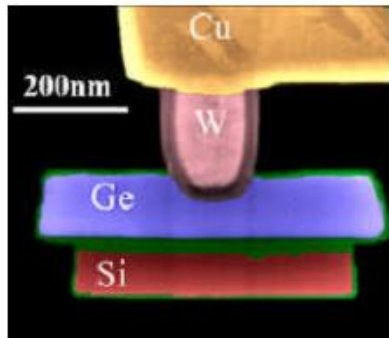
- Different Mechanisms
 - Forward PIN
 - Reverse PIN



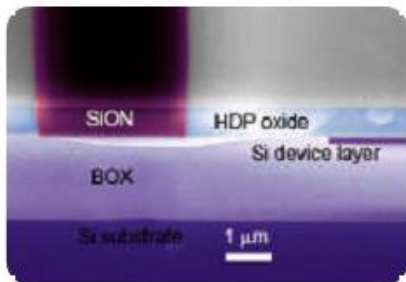
PN diode in reverse bias

CMOS COMPATIBLE FABRICATION

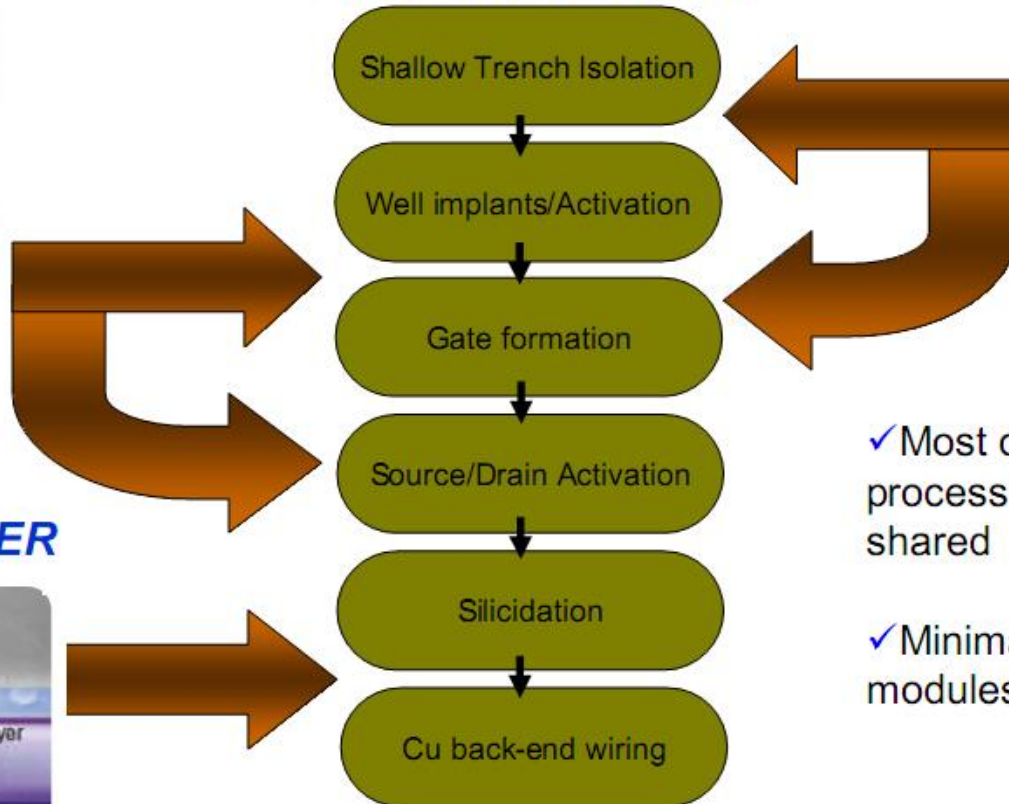
DETECTOR



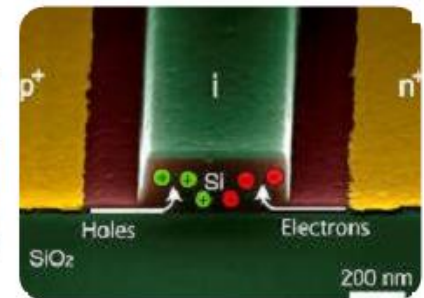
FIBER COUPLER



FEOL CMOS FLOW



MODULATOR

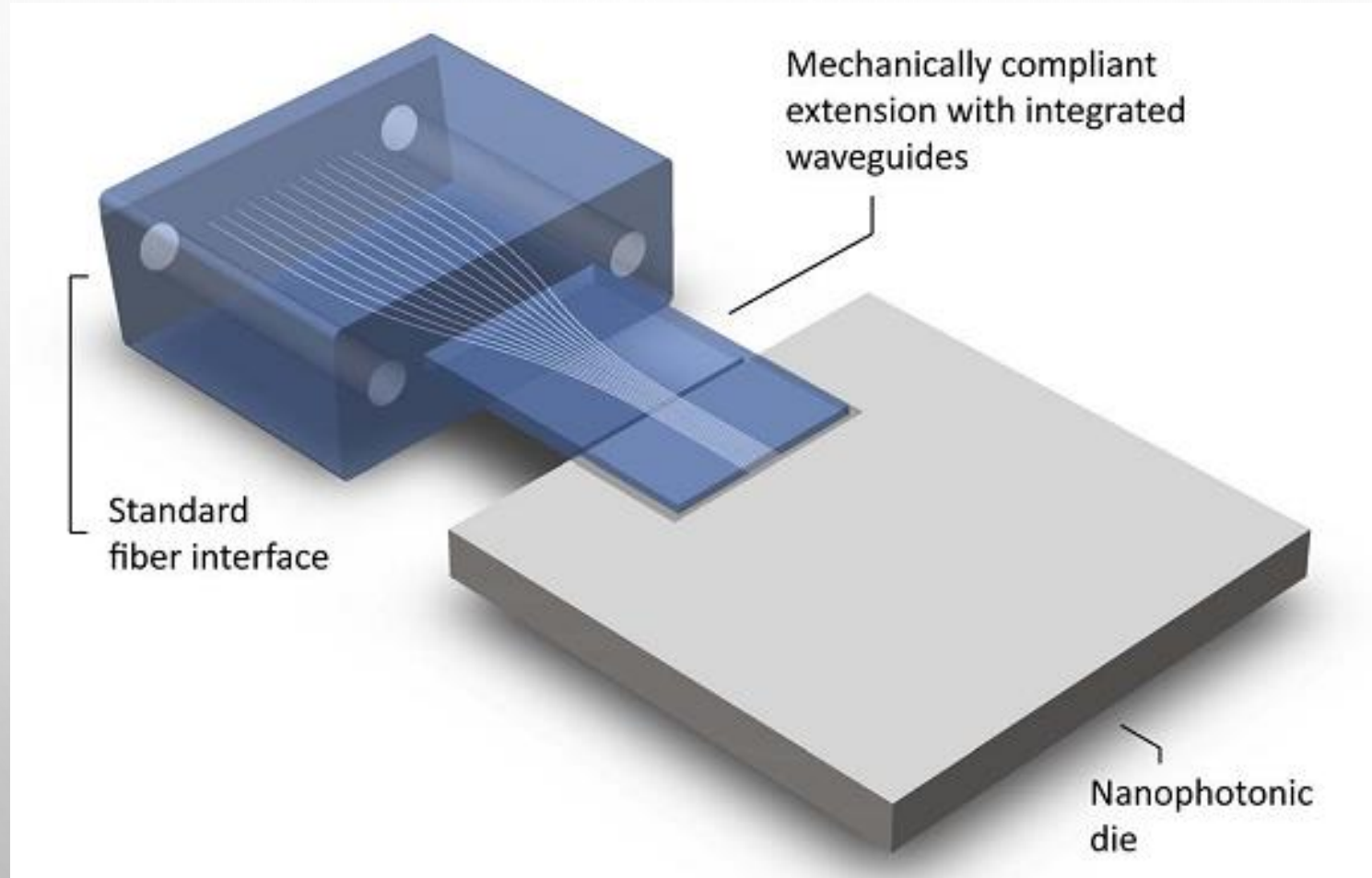


✓ Most of the mask levels and processing modules are shared

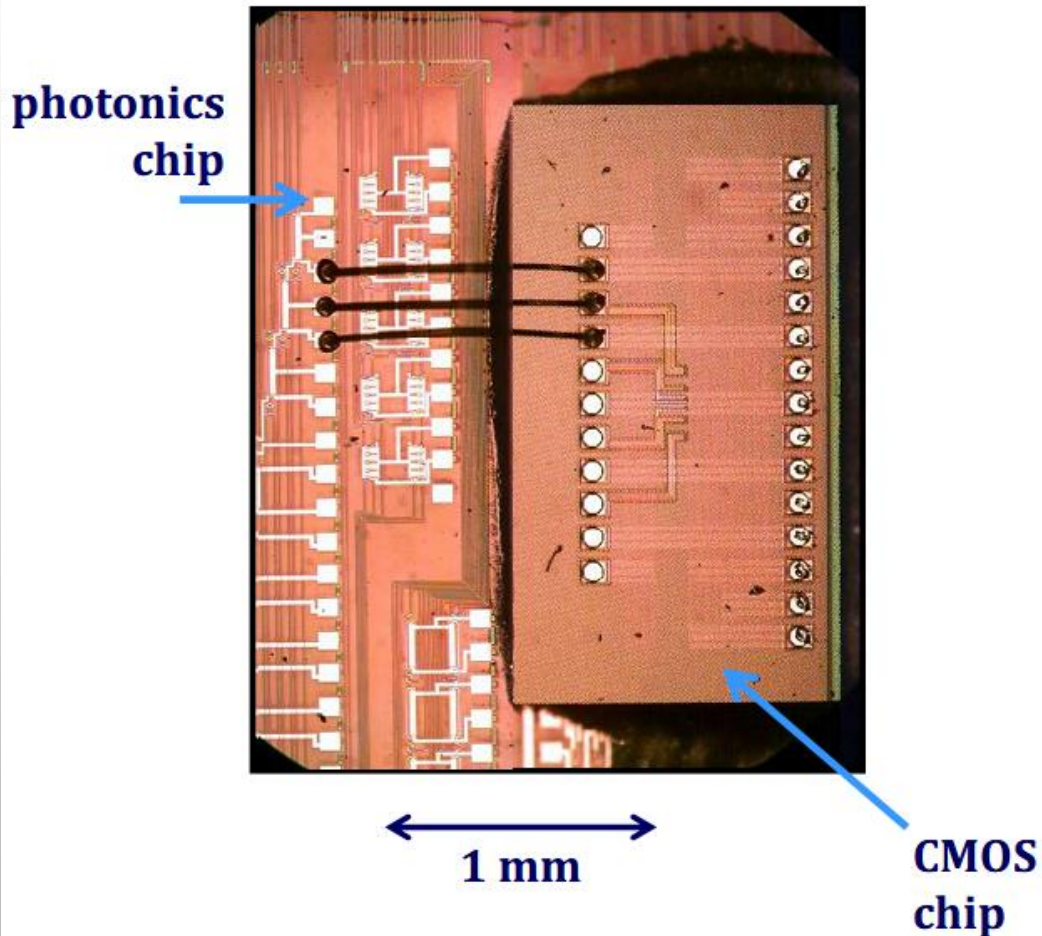
✓ Minimal additional photonics modules added

Photonics as a new feature in standard CMOS

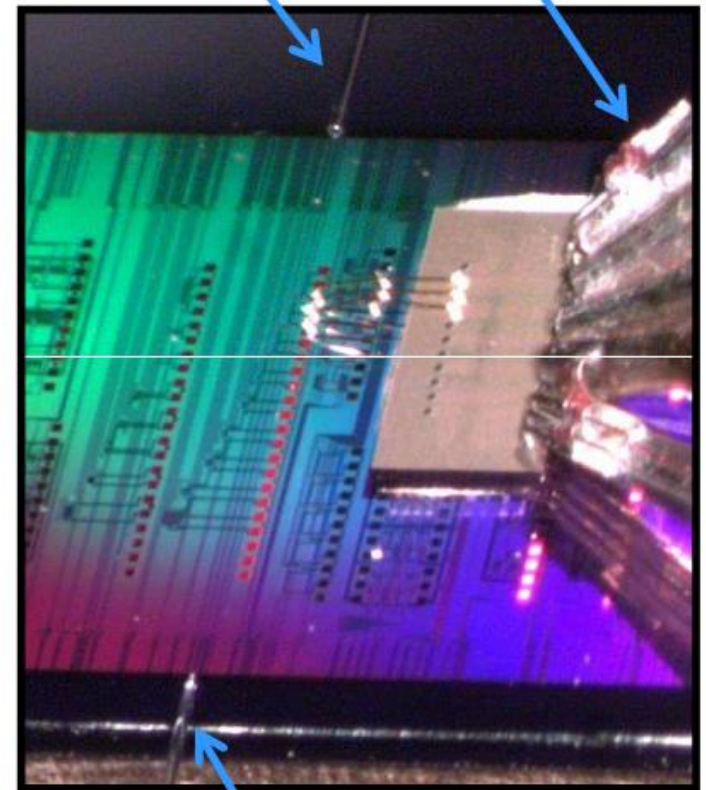
FIBER TO WAVEGUIDE COUPLING (PACKAGING)



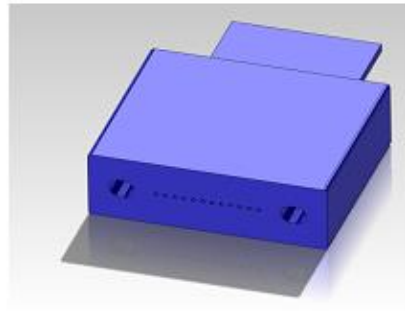
PACKAGING (PUTTING IT ALL TOGETHER)



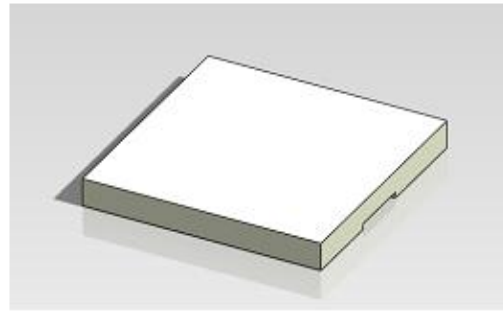
optical fiber probe
electrical probe



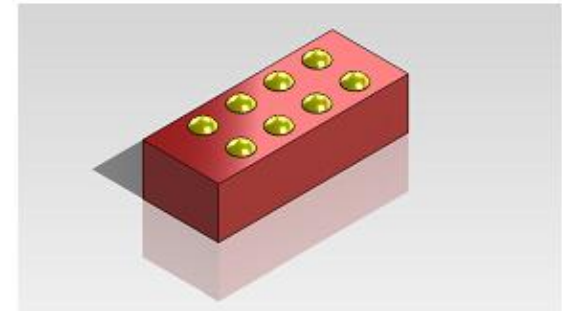
PACKAGING (PUTTING IT ALL TOGETHER)



Fiber ferrule



SiPh die

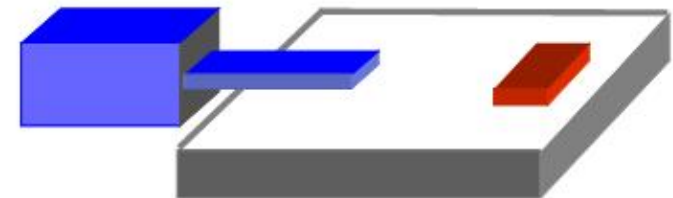
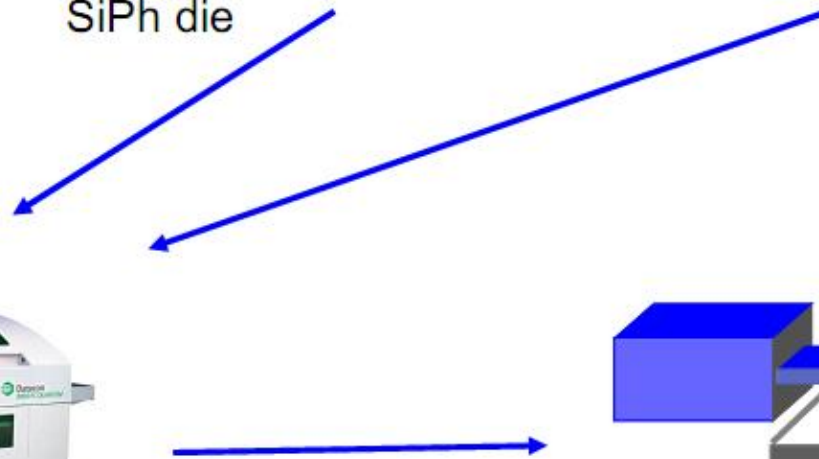


DFB laser array

2013



Pick & Place
Passive alignment of optical components



First level package

PACKAGING (PUTTING IT ALL TOGETHER)



Automated assembly

IBM Watson, NY USA
Interface design, Si fabrication

Tymon Barwicz and team

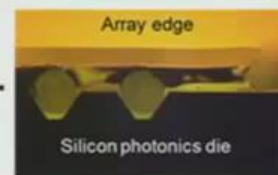
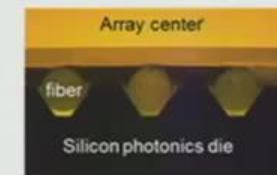
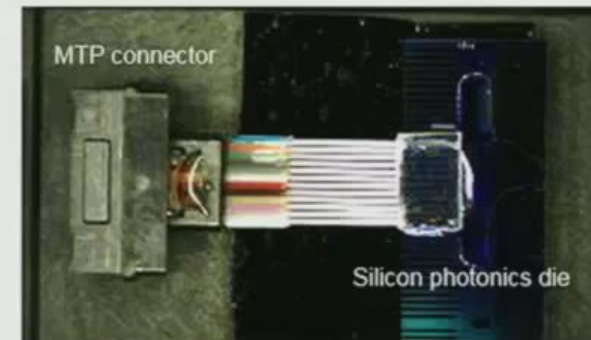
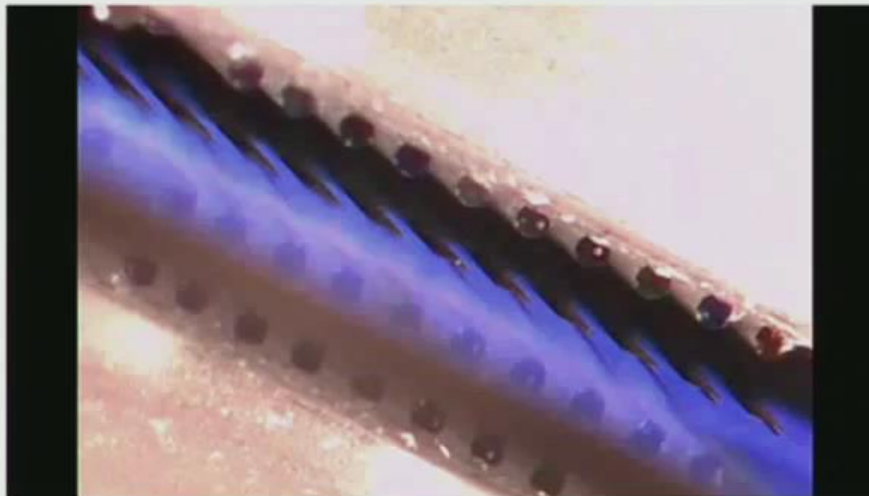
IBM Research - Tokyo
Ribbon to ferrule assembly

Yoichi Taira and team

IBM Bromont – C2MI
Ribbon to Si assembly

Paul Fortier and team

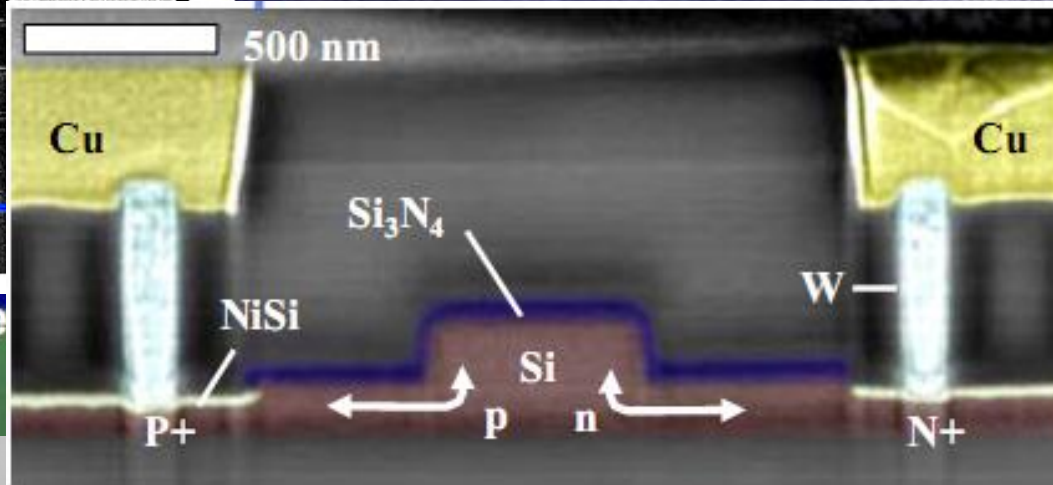
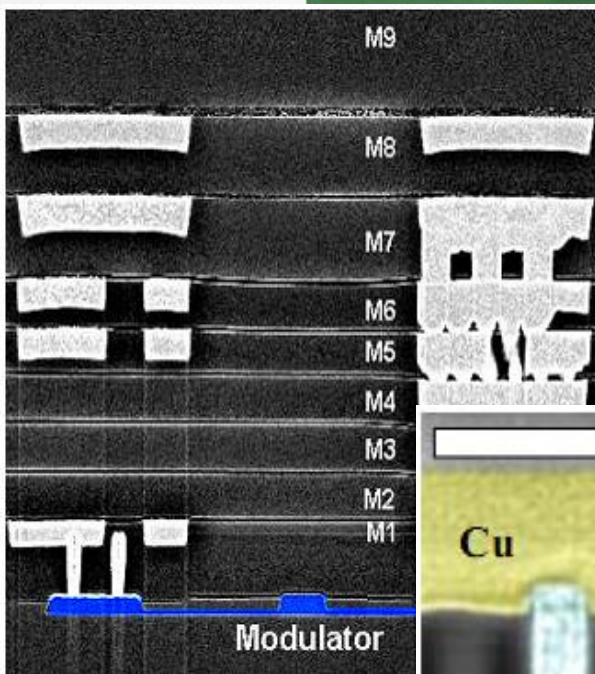
Partners



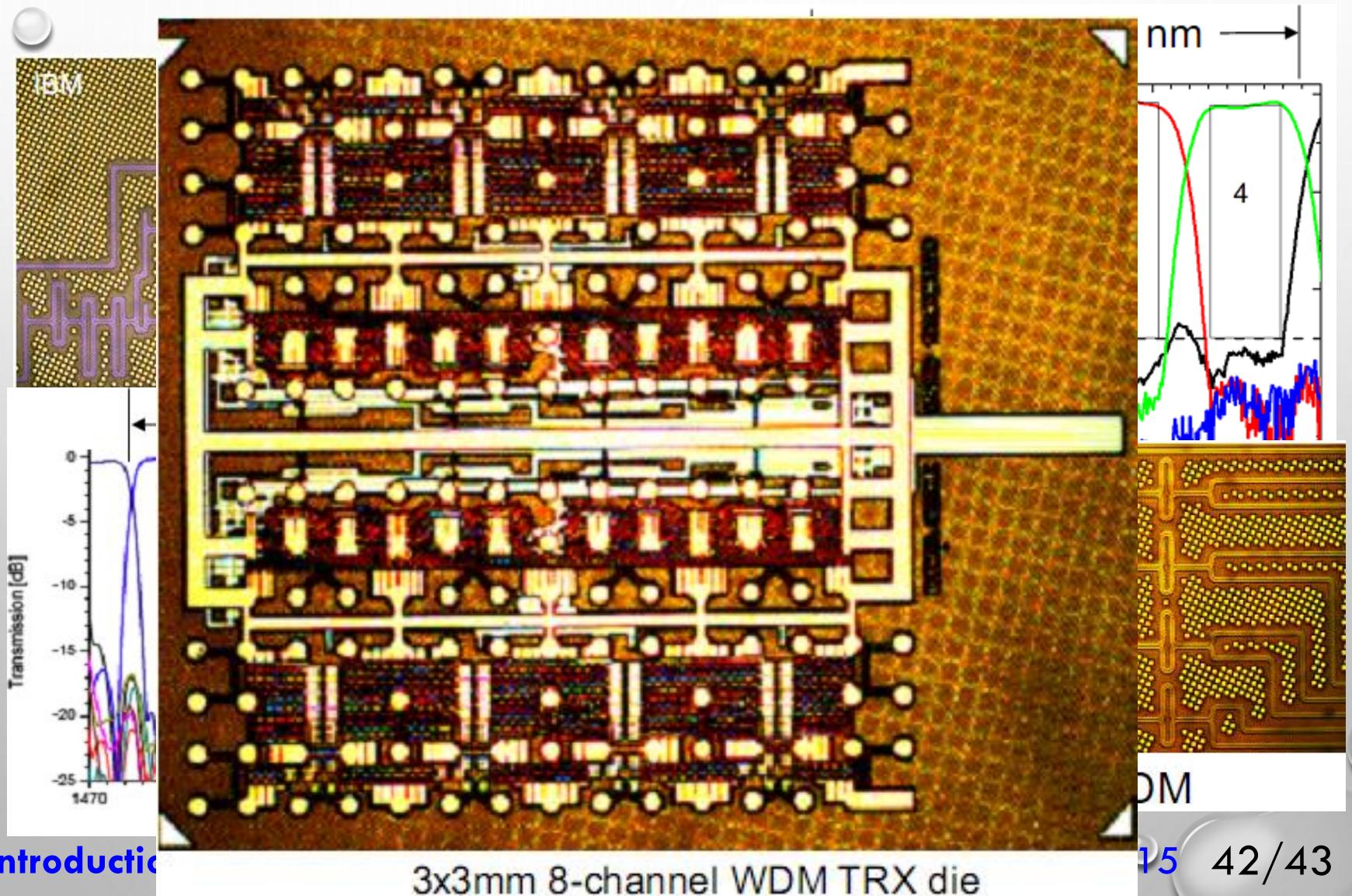
- ✓ Bandwidth 1260-1360nm
- ✓ Insertion loss -1.3dB
- ✓ Worst PDL 0.6dB
- ✓ Return loss -30dB

T. Barwicz et al., IEEE ECTC, 2015.
T. Barwicz, et al OFC 2015

OEIC SYSTEM EXAMPLES



OEIC SYSTEM EXAMPLES

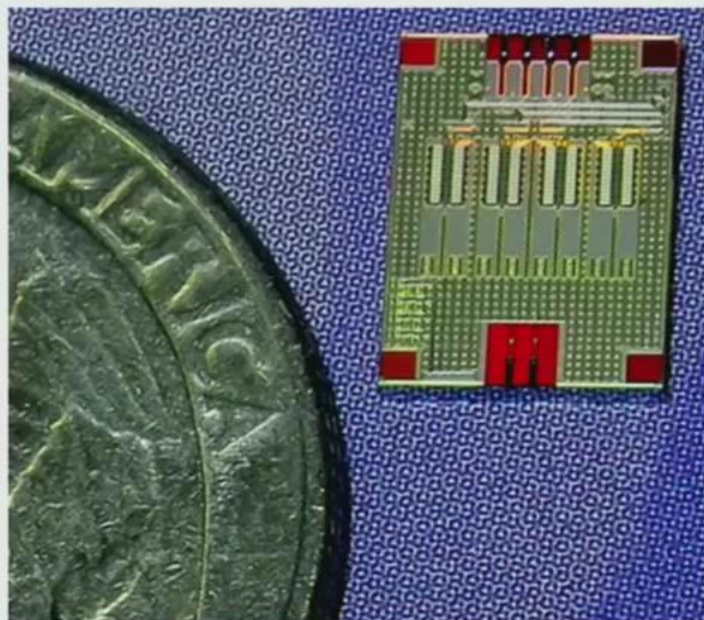


OEIC EXAMPLES



Reference Design: 4x25G CWDM Transceiver

- ✓ 4x25G Ge PD RX
- ✓ 4x25G TW MZITX
- ✓ CWDM 1310nm
- ✓ Polarization S&R
- ✓ DAC/ADC controllers
- ✓ SMF coupling
- ✓ Packaging structures



- ✓ Monolithic single-die 100Gbps silicon nanophotonics transceiver
- ✓ Fabrication tolerant and manufacturable